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Key elements in NEMO to quantitative nano-scale carrier transport analysis in semiconductors

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Thanks to:
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NEMO 1-D

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R. Chris Bowen, Texas Instruments / JPL / Texas Instruments

Tim Boykin, U Alabama in Huntsville

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NEMO 3-D / Synthesis

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Seungwon Lee, JPL

Paul von Allmen, JPL

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R. Chris Bowen, JPL

Thomas A. Cwik, JPL

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Outline: Key Elements to NEMO

- **NEMO Goal:**
  - Quantitative design and synthesis of resonant tunneling diodes (RTD's).
  - Faster simulation than experimental turn-around (1 week).
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  - Scattering - origin of the valley current.
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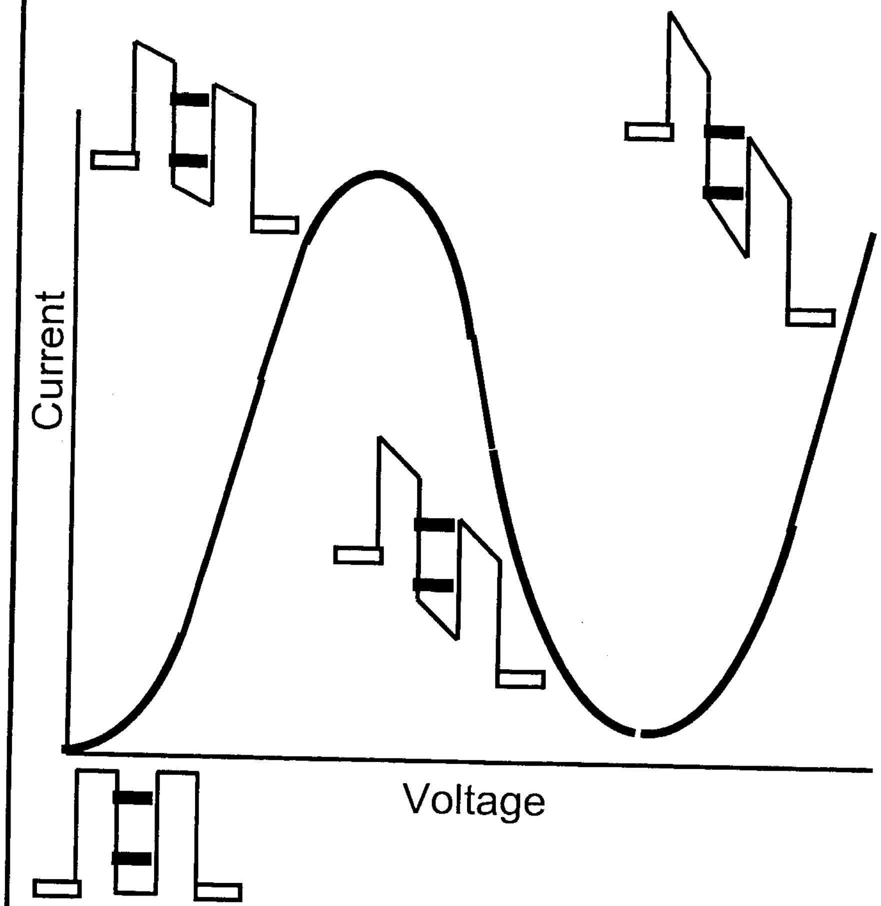
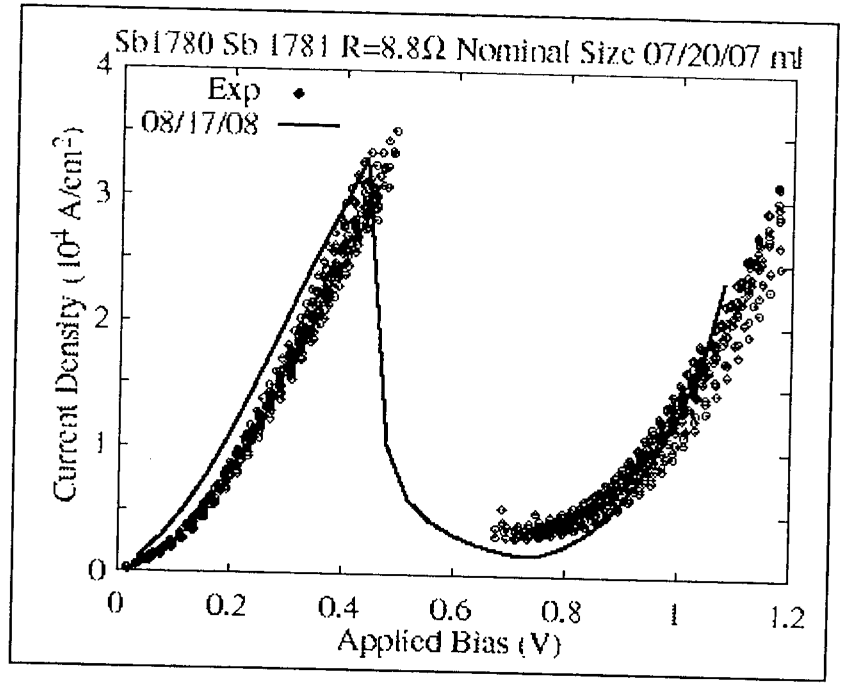
  - Treatment of extended contact regions
  - Full bandstructure - Empirical tight binding: sp3s*, sp3d5s*
    - Non-parabolicity, complex band warping, indirect gaps
- **Putting it all together**
  - NEMO - testmatrix
  - **The next step: automated analysis and SYNTHESIS**

Resonant Tunneling Diode



Conduction band diagrams for different voltages and the resulting current flow.

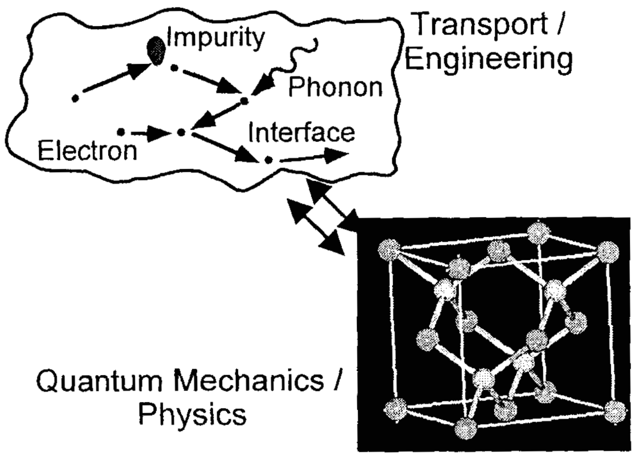


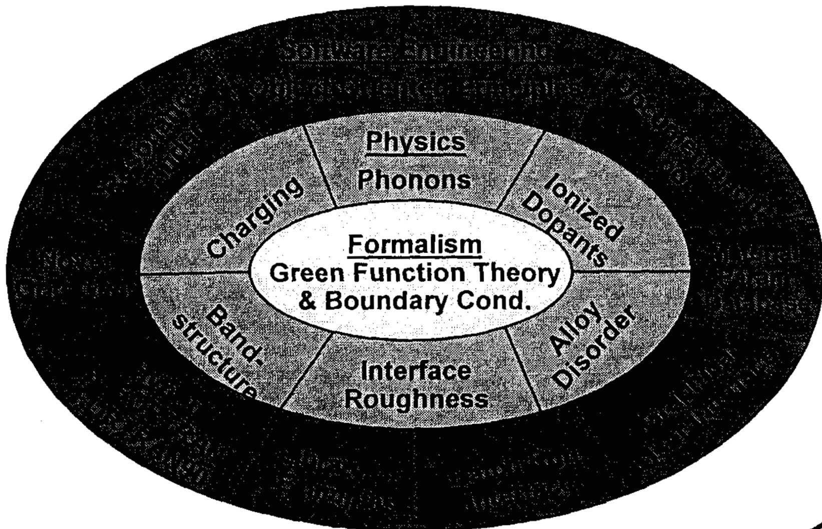
12 different I-V curves: 2 wafers, 3 mesa sizes, 2 bias directions

50nm	1e18	InGaAs
7 ml	nid	InGaAs
7 ml	nid	AlAs
20 ml	nid	InGaAs
7 ml	nid	AlAs
7 ml	nid	InGaAs
50 nm	1e18	InGaAs

NEMO:
A User-friendly Quantum Device Design Tool

- NEMO 1-D was developed under a NSA/NRO contract to Texas Instruments and Raytheon from '93-'98 (>50,000 person hours, 250,000 lines of code).
- NEMO 1-D maintained and NEMO 3-D developed at JPL '98-'02 (>12000 person hours) under NASA funding. Since '02 NSA and ONR funding.
- NEMO is THE state-of-the-art quantum device design tool.
  - First target: transport through resonant tunneling diodes (high speed electronics).
  - Second target: electronic structure in realistically large nano devices (detectors).
  - Newly set target: qbit device simulation.
- Bridges the gap between device engineering and quantum physics.
- Based on Non-Equilibrium Green function formalism NEGF - Datta, Lake, and Klimeck.
- Used at Intel, Motorola, HP, Texas Instruments, and >10 Universities.





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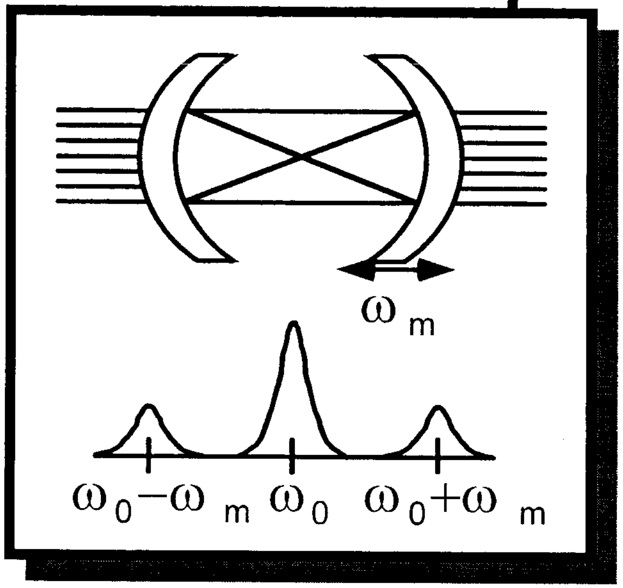
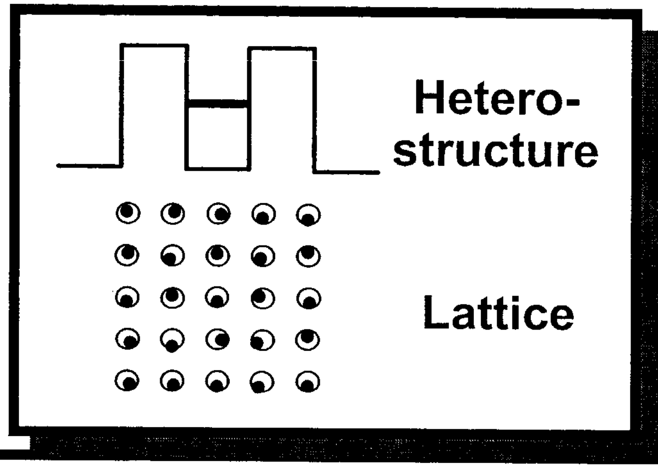
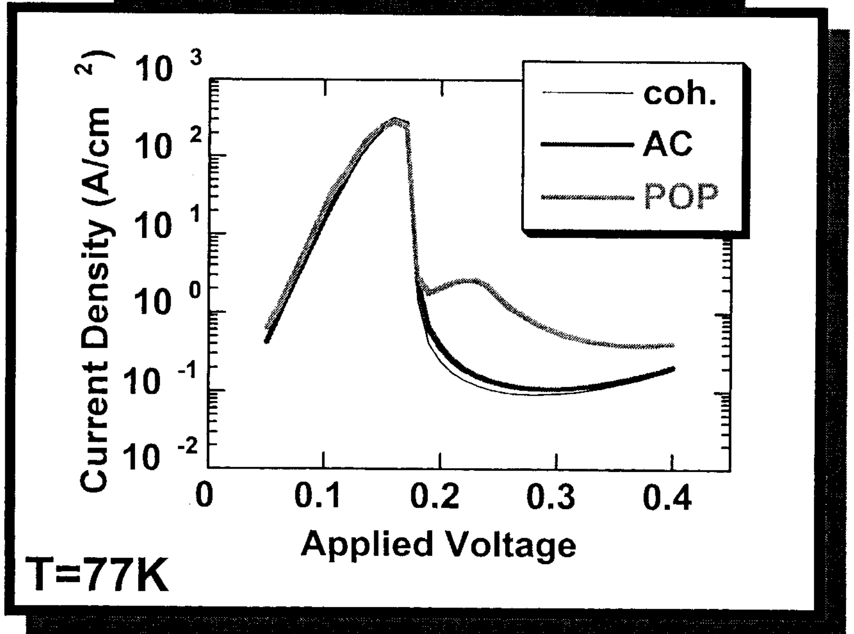
Electron-Phonon Interactions
Coupled Resonators



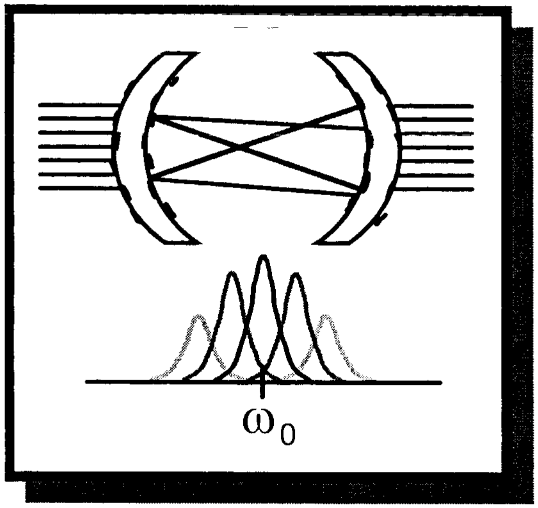


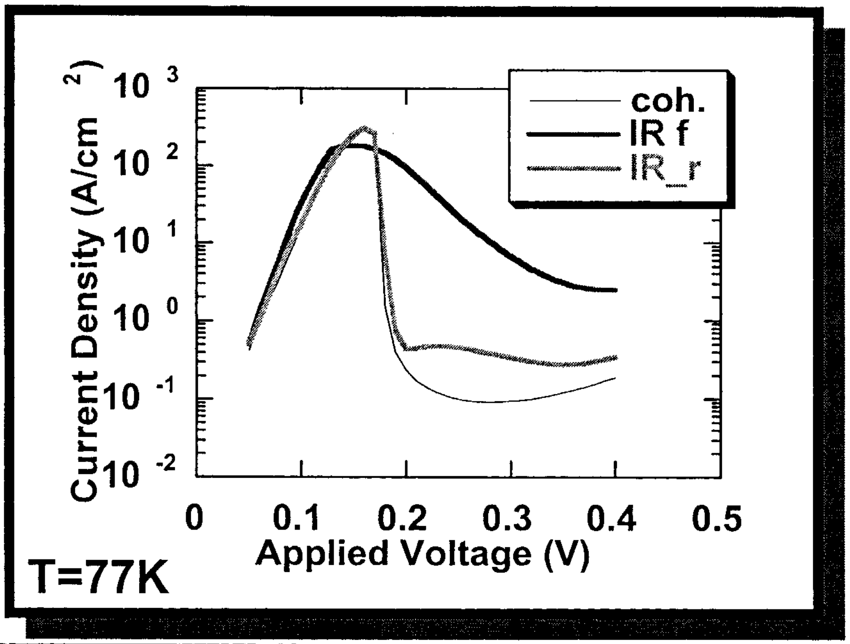
Self-consistent Born (infinite sequential scattering) treatment of acoustic phonon-scattering

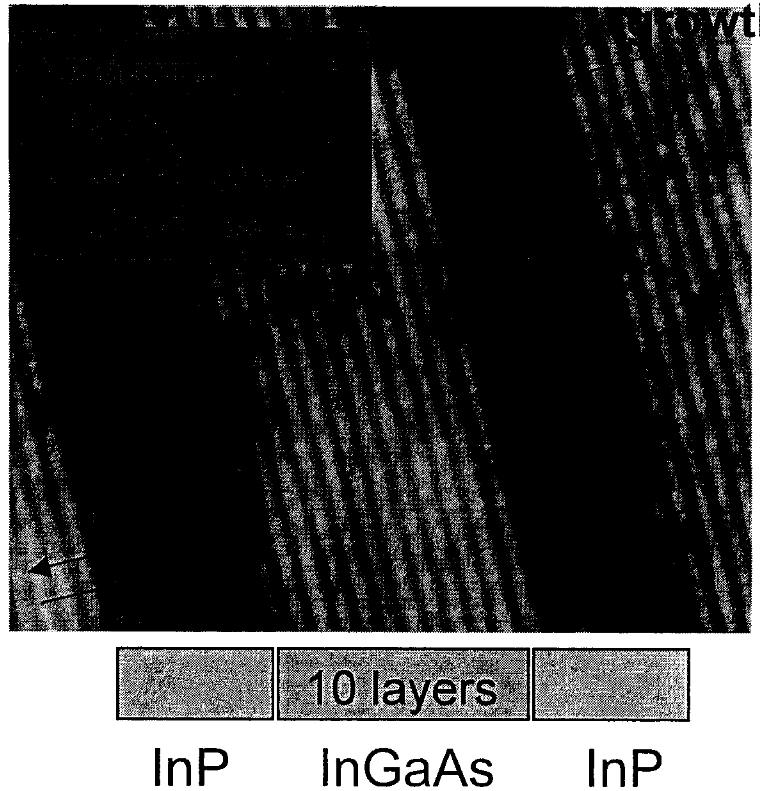
Single sequential scattering treatment of polar optical phonon scattering



Interface Roughness Scattering

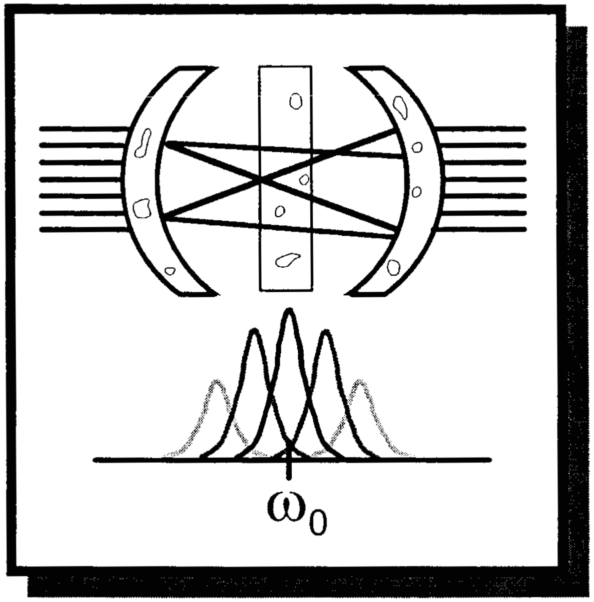




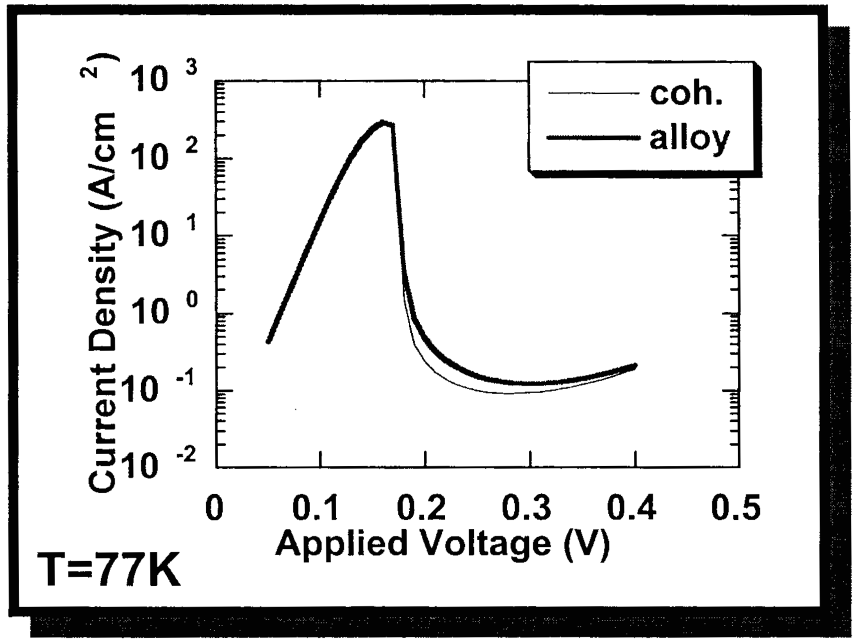


Self-consistent Born (infinite sequential scattering) treatment of IR-scattering

Alloy (Disorder) Scattering

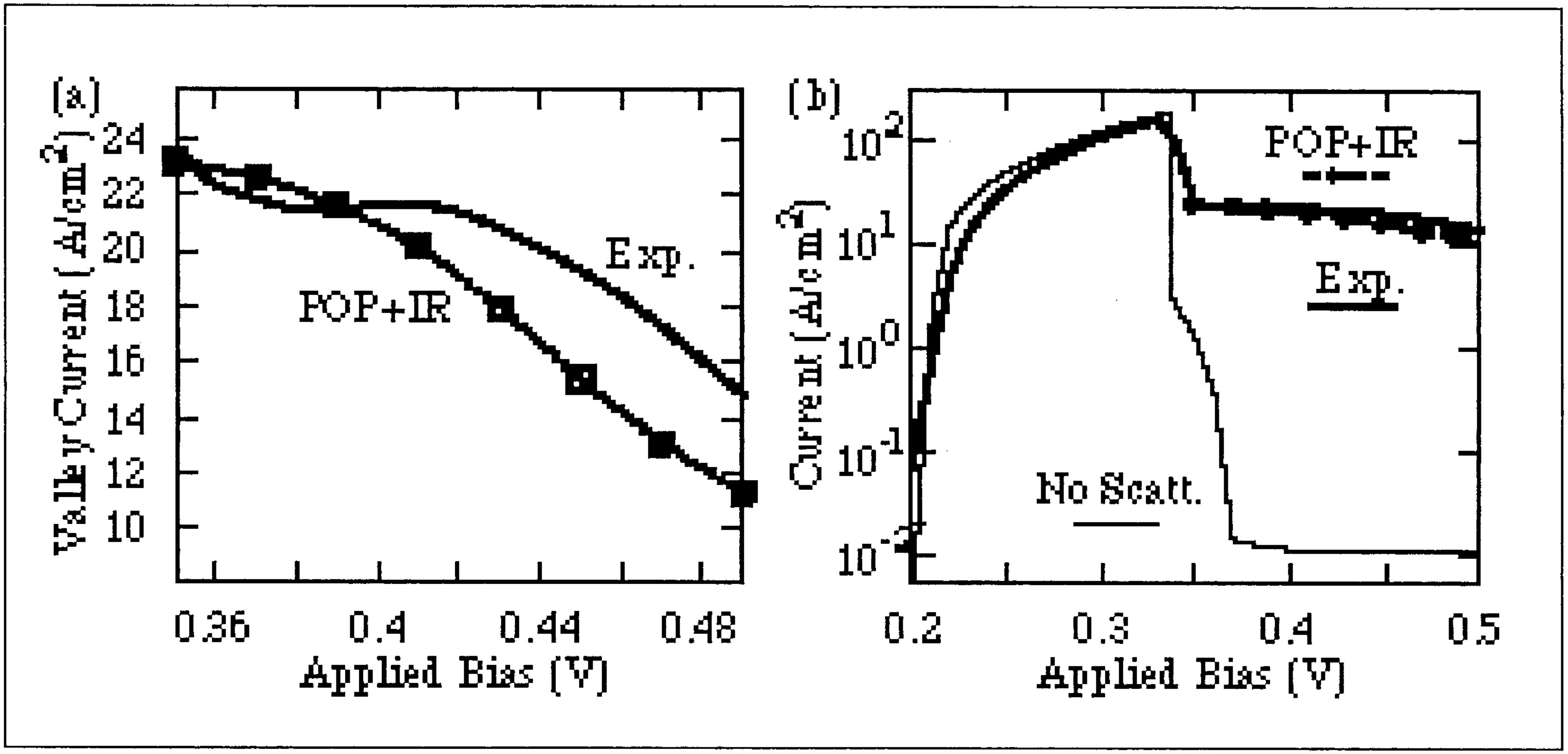


Disorder in the mirrors or the gain medium will spread out the resonator spectrum



Self-consistent Born (infinite sequential scattering) treatment of alloy-scattering

Tow Temperature: Polar Optical Phonon and Interface Roughness Scattering



scattering raises valley current by several orders of magnitude

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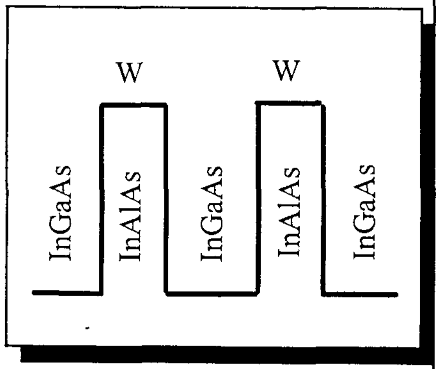
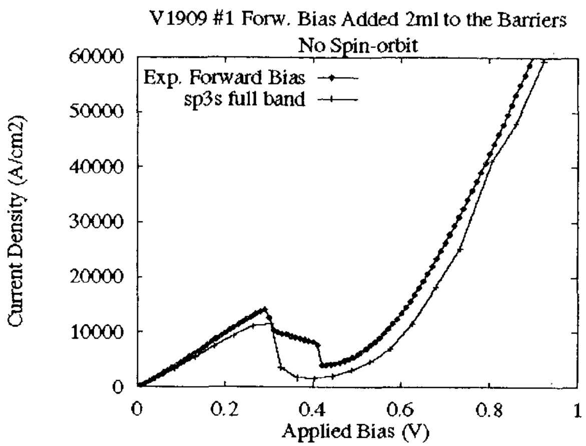
Charge Accumulation/Depletion

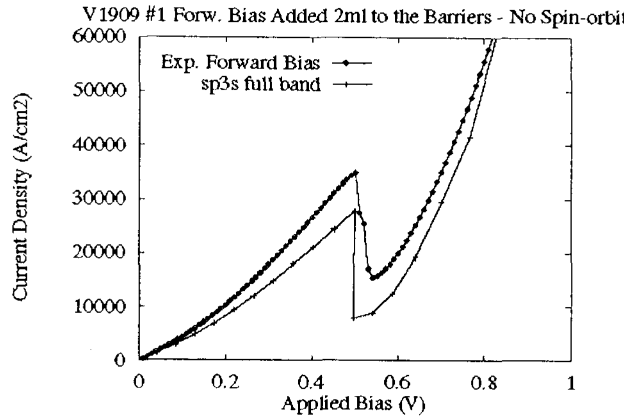
Vary Well Width



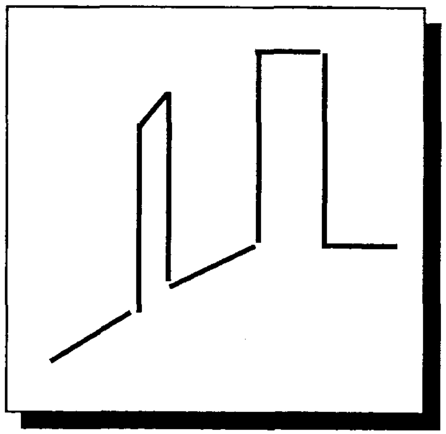
asymmetric device:
35/47/47 A [4]

Asymmetric Device

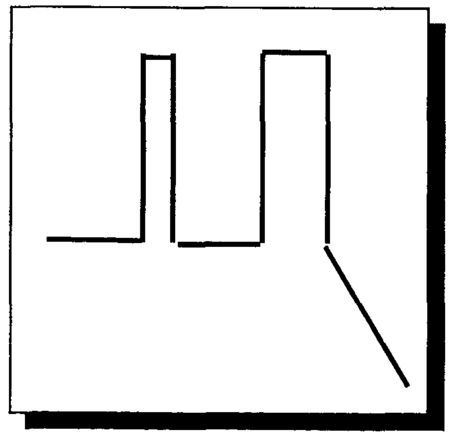




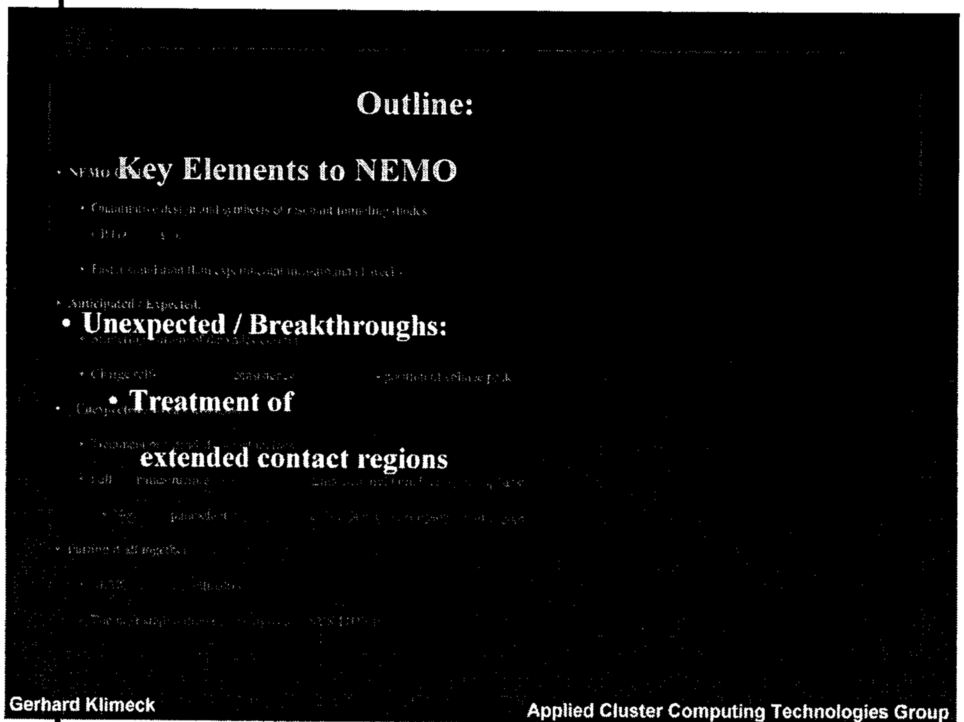
Reverse Bias



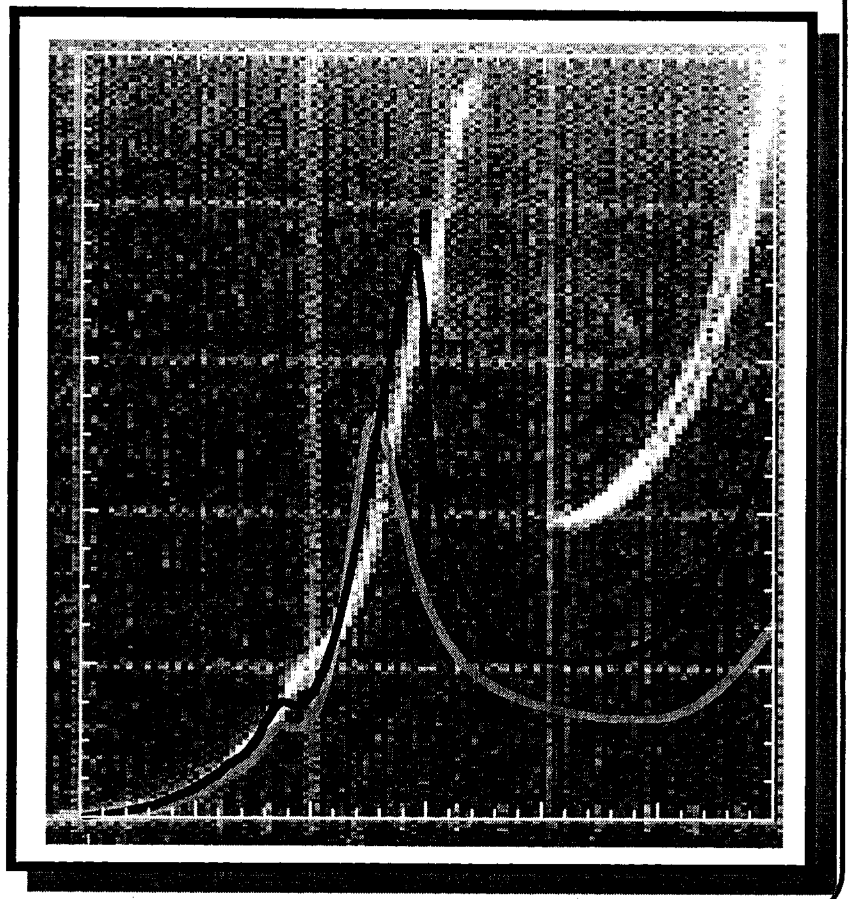
Forward Bias



Symmetric RTD's: Charge Self-Consistency Still Important!

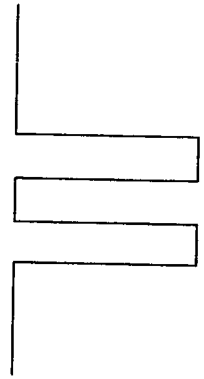


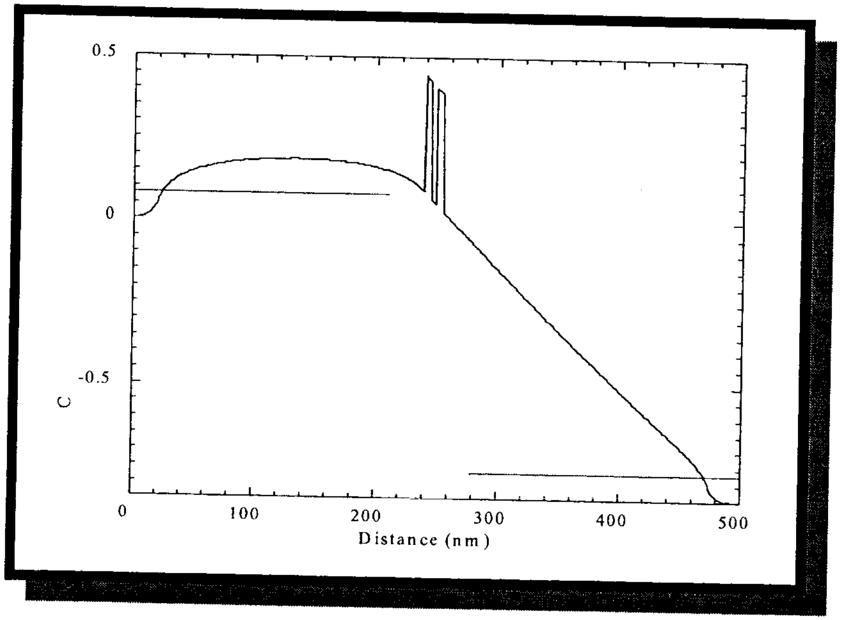
——Thomas-Fermi
——Hartree

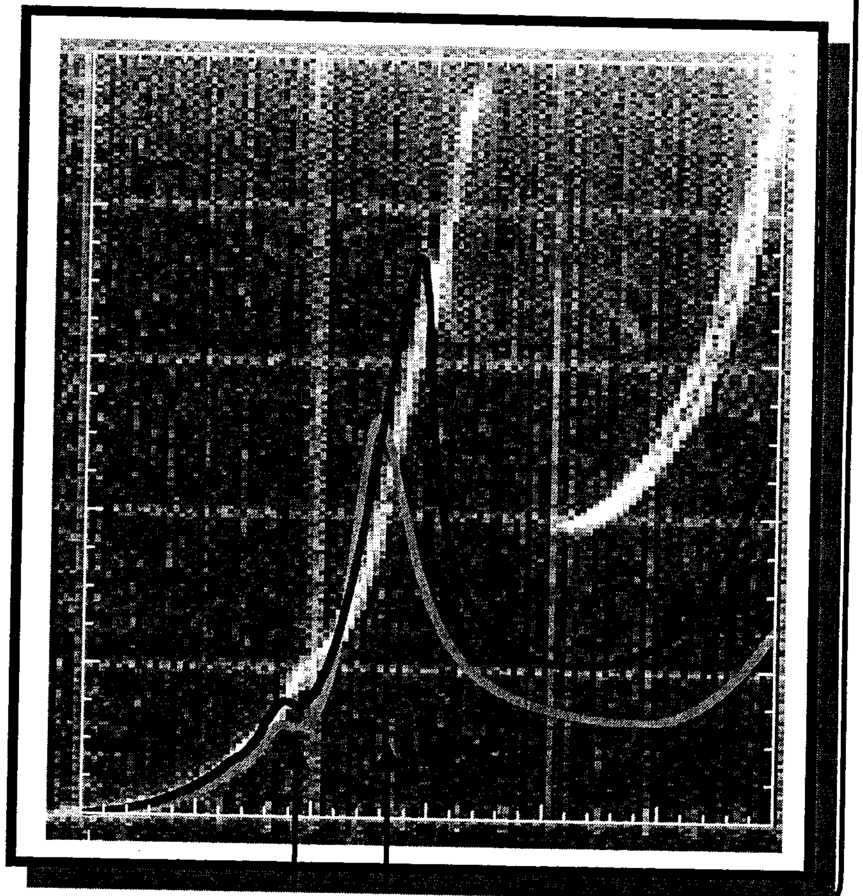


Modeling of a Typical GaAs/$Al_{0.4}Ga_{0.6}As$ RTD

20 nm GaAs $N_D = 2\ 10^{18}\ cm^{-3}$
200 nm GaAs $N_D = 2\ 10^{15}\ cm^{-3}$
18 nm GaAs
5 nm $Al_{0.4}Ga_{0.6}As$
5 nm GaAs
5 nm $Al_{0.4}Ga_{0.6}As$
18 nm GaAs
200 nm GaAs $N_D = 2\ 10^{15}\ cm^{-3}$
20 nm GaAs $N_D = 2\ 10^{18}\ cm^{-3}$







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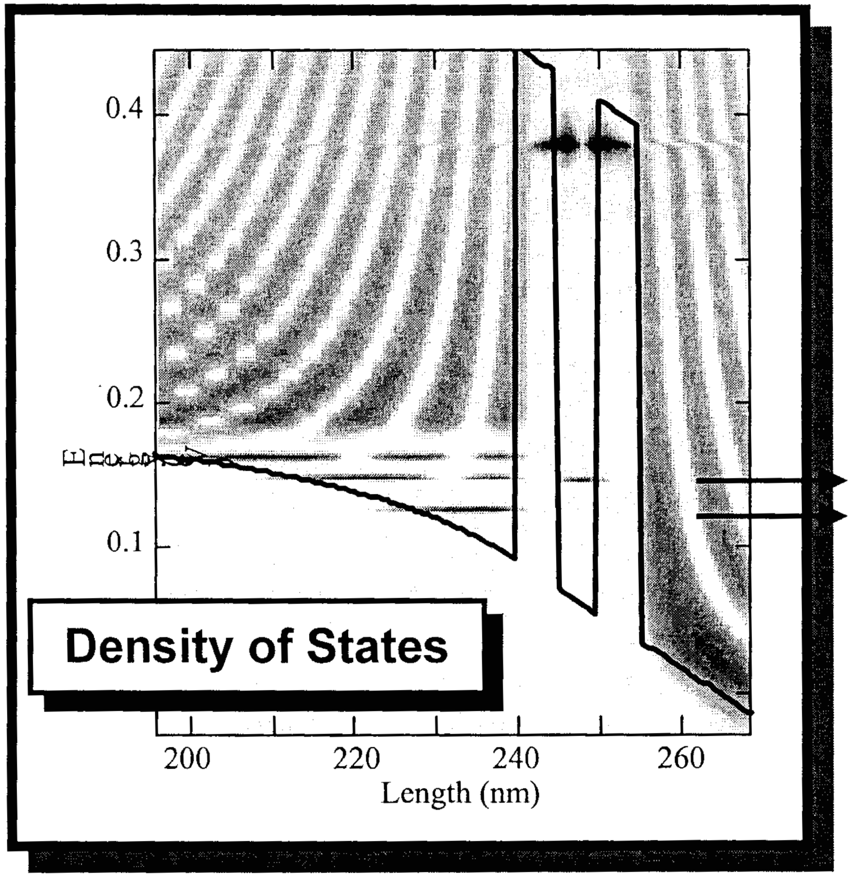
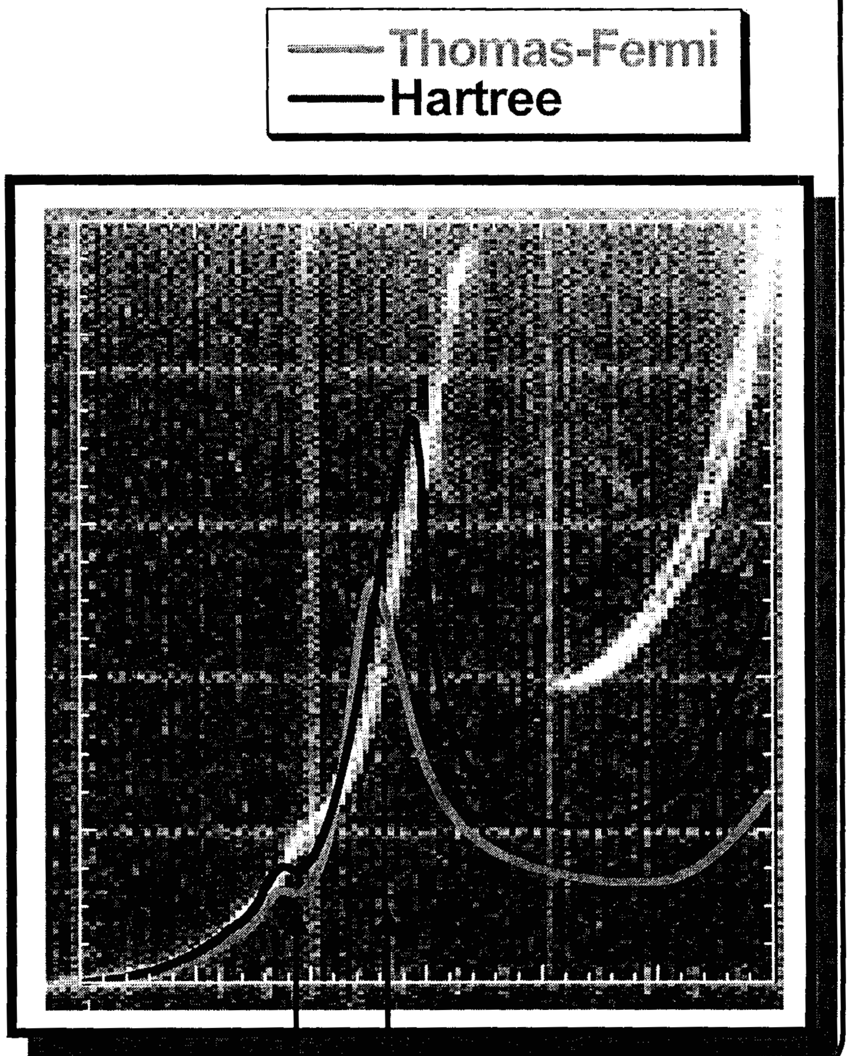
Modeling of a Typical $GaAs/Al_{0.4}Ga_{0.6}As$ RTD

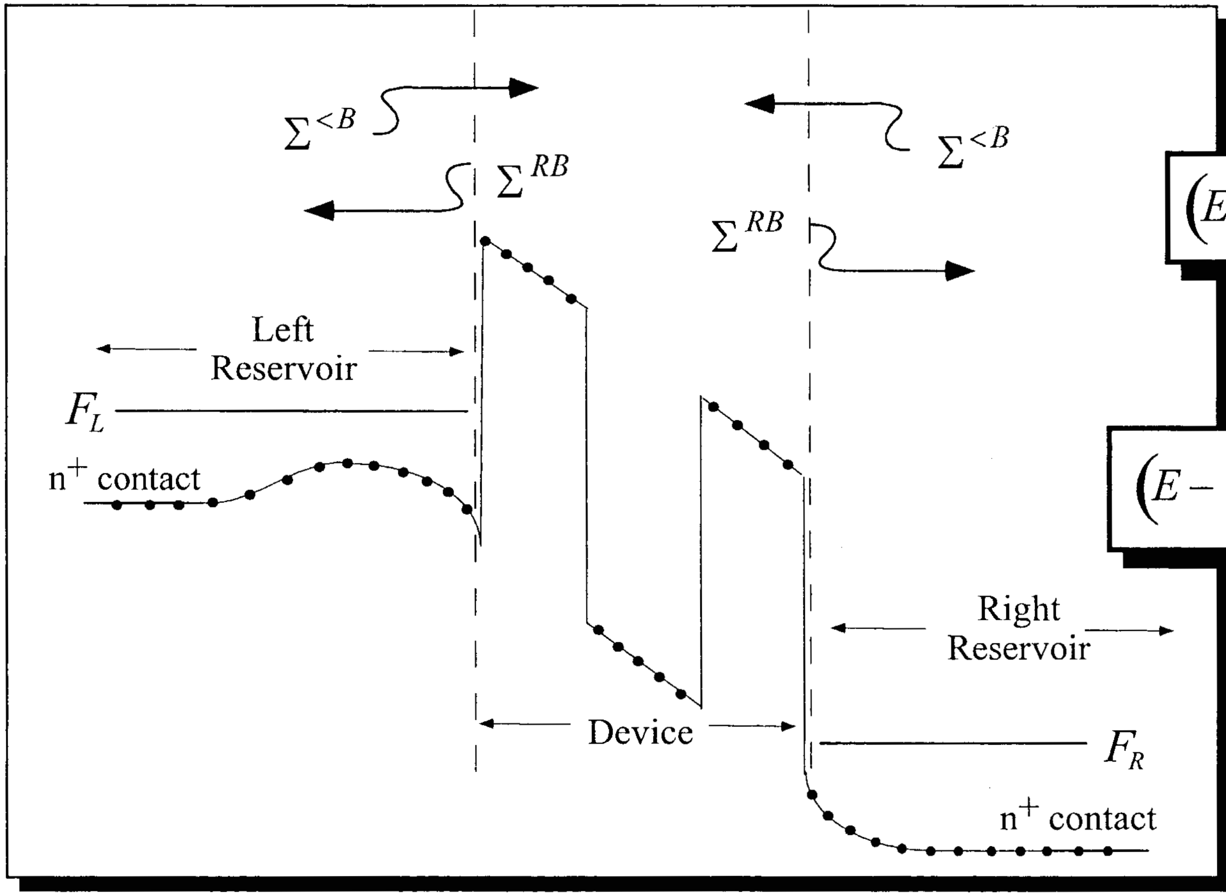




Carrier Injection from:
- Emitter bound states
- Continuum states.

Generalized Boundary Conditions: Boundaries as a Scattering Problem

- Left and right regions are treated as reservoirs.
- Quantum structure of reservoirs is included exactly.



Dynamics

$$\left(E - H_0 - \Sigma^{RB}\right)G^R = 1$$

$$\left(E - H_0 - \Sigma^{RB}\right)G^< = \Sigma^{<B} G^A$$

Kinetics

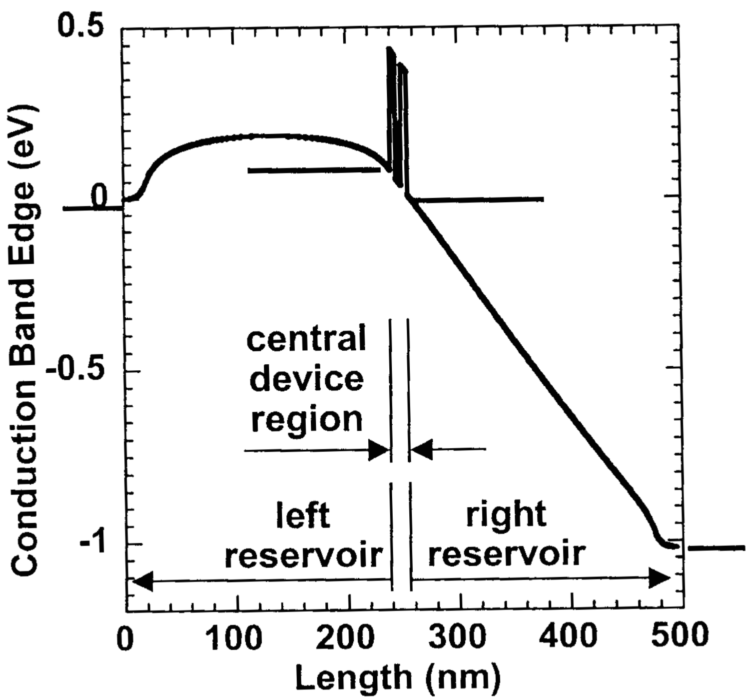
Treatment of the Electron Reservoirs

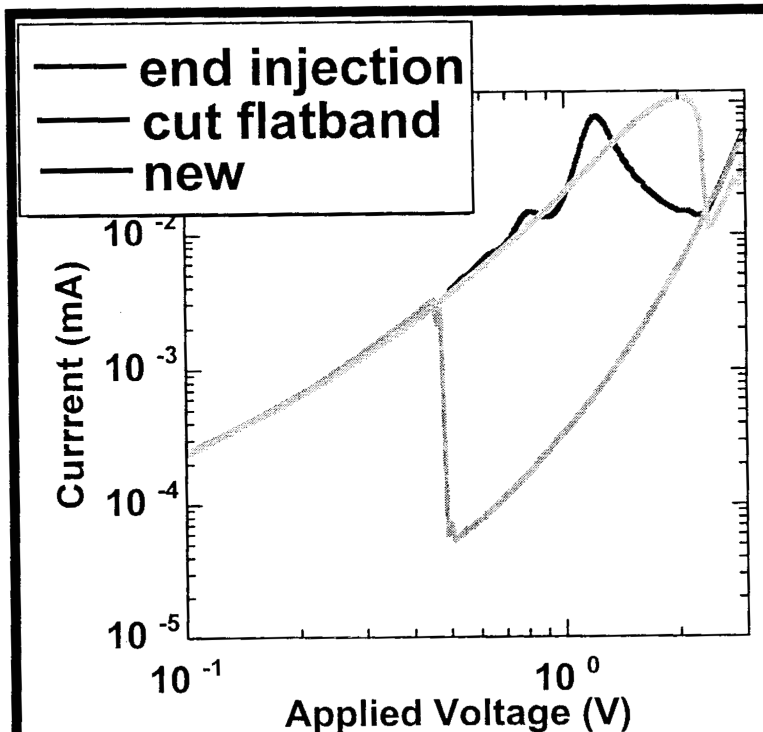
Typical Methods:

- Injection from reservoirs with flat bands

New Method:

- Injection of carriers from reservoirs with bent bands
- Modified densities of states





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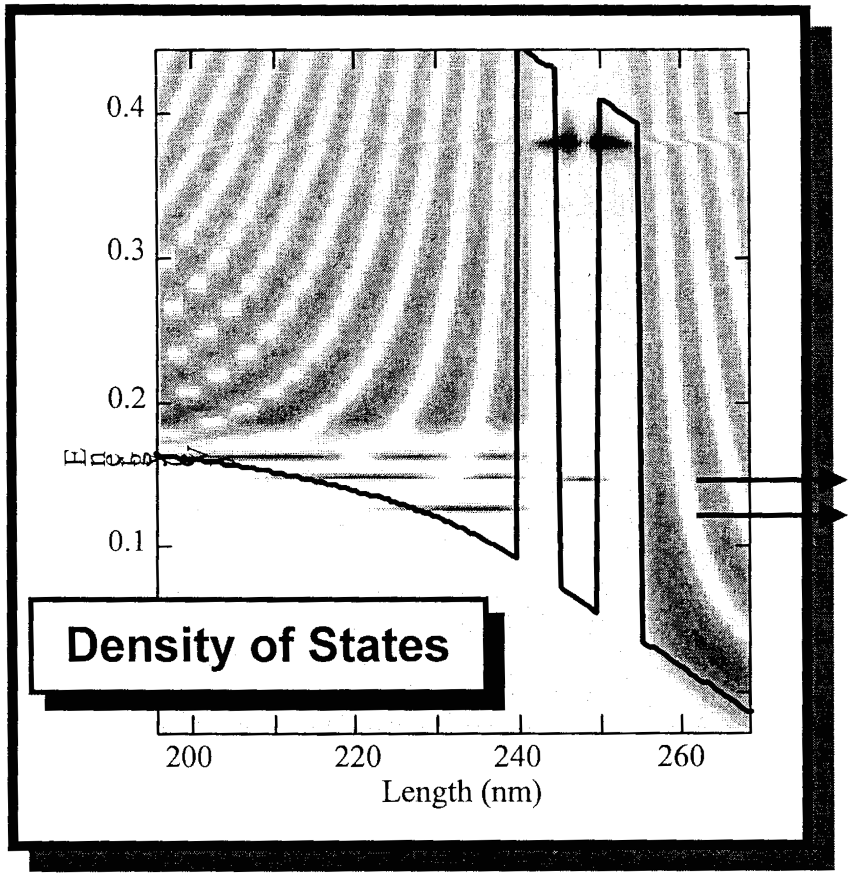
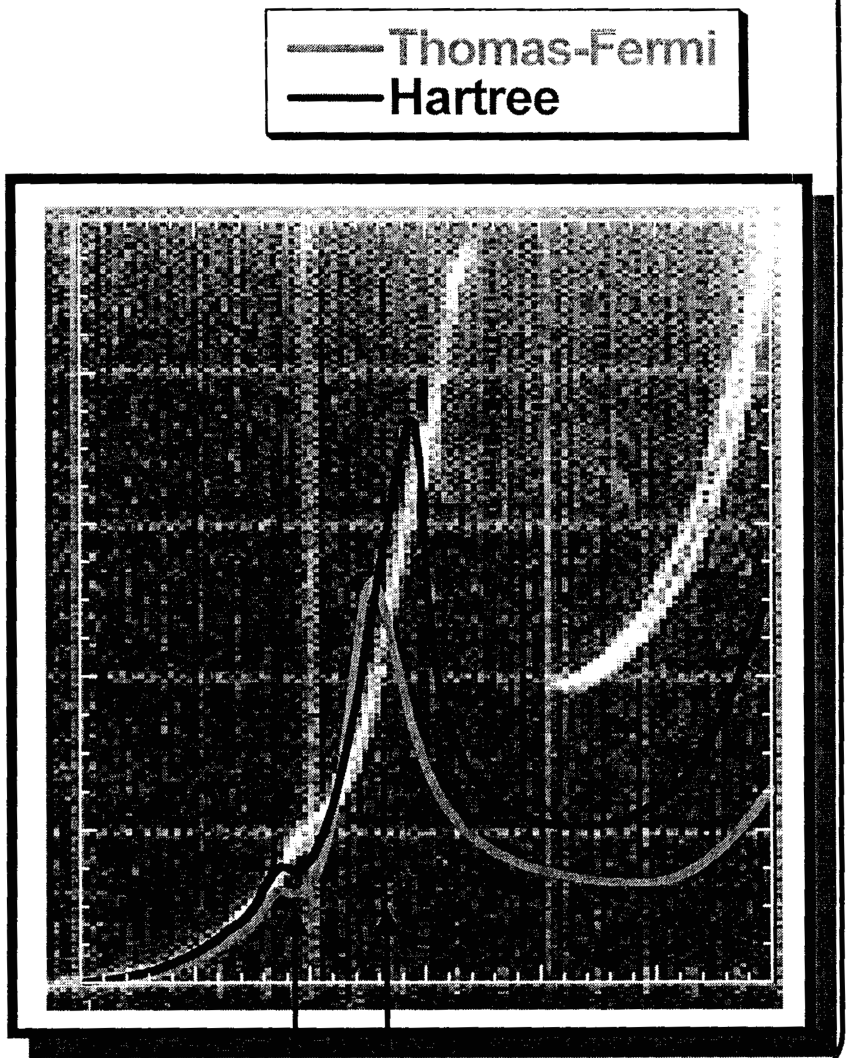




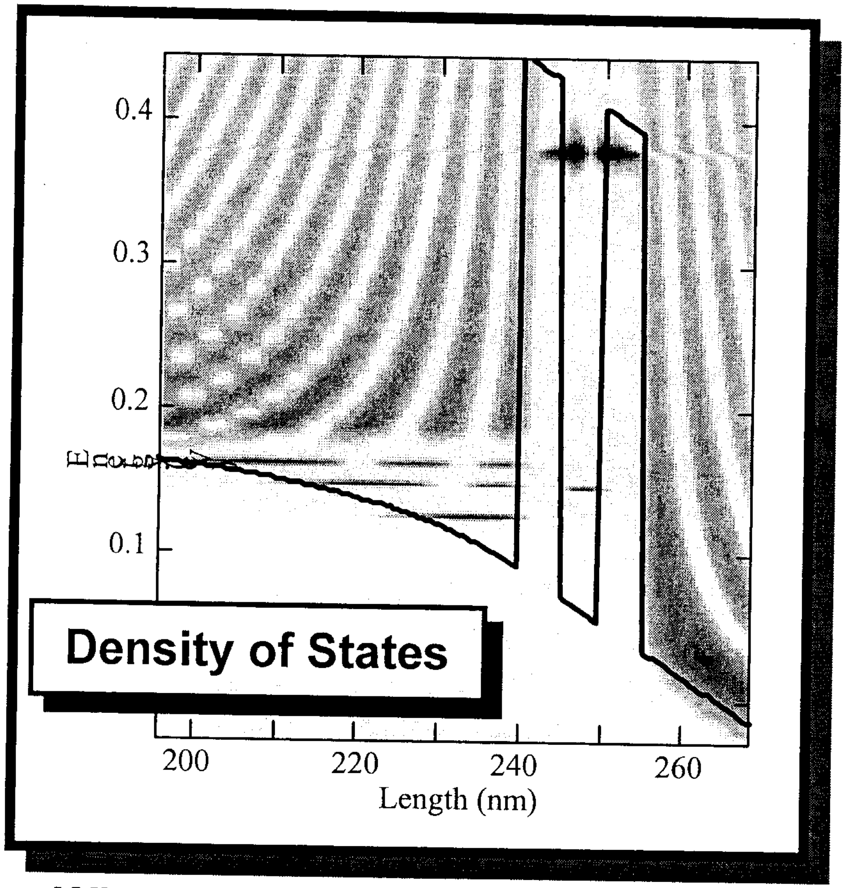
Where does the valley current current come from?

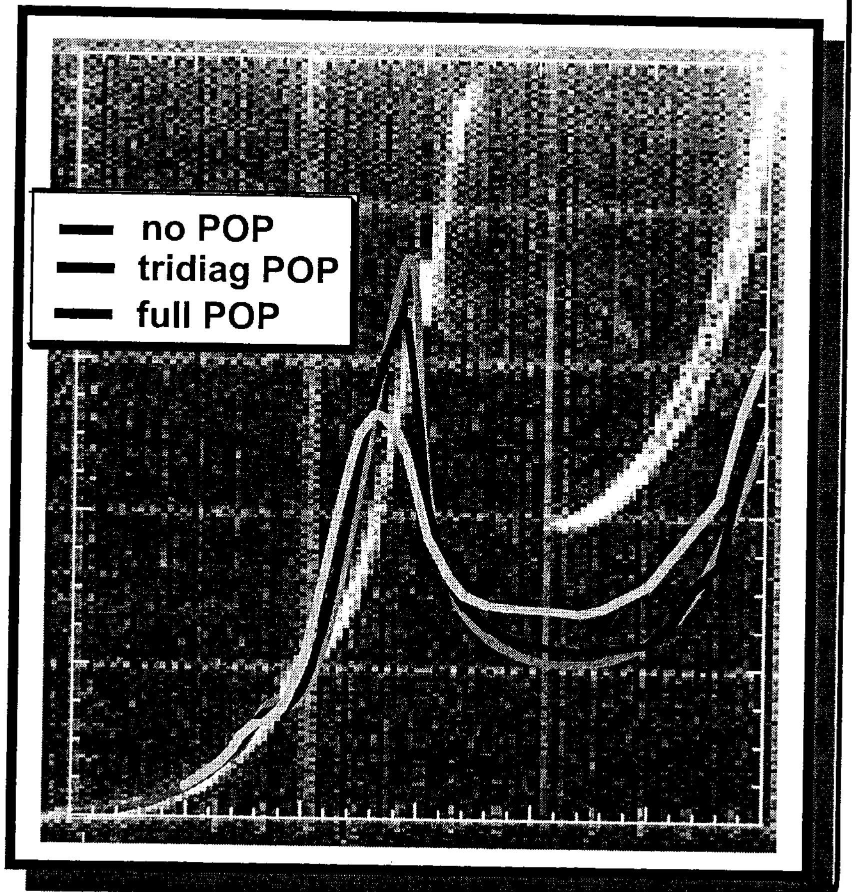
Self-consistency helps - not enough

Modeling of a Typical $GaAs/Al_{0.4}Ga_{0.6}As$ RTD

Single band with scattering

POP = Polar Optical Phonons





Where does the valley current current come from?

POP is the only efffective scattering mechanism - not enough

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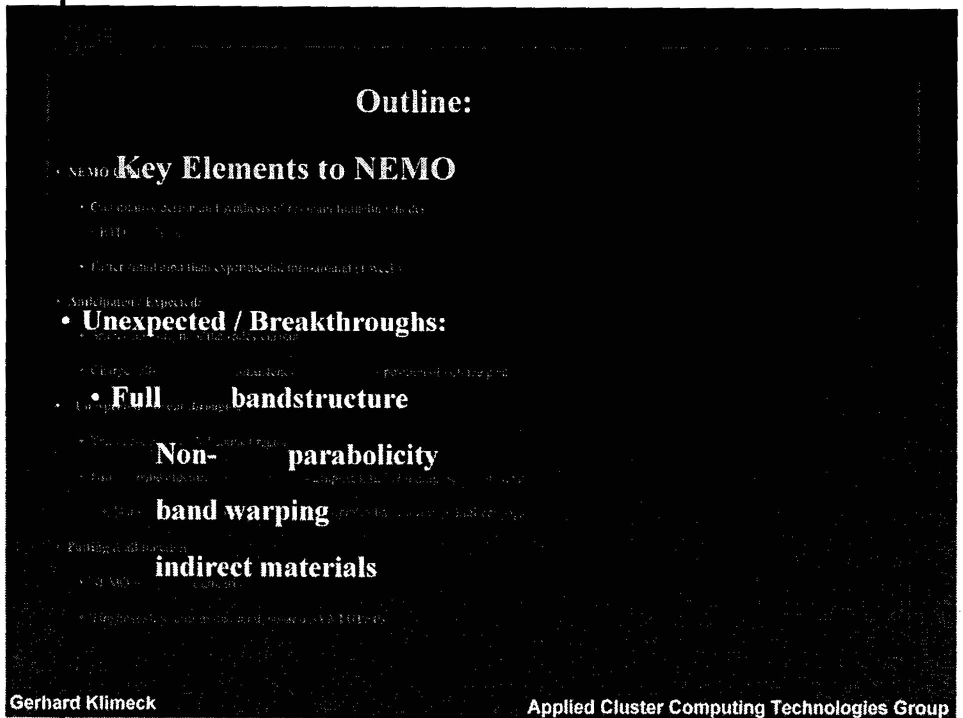

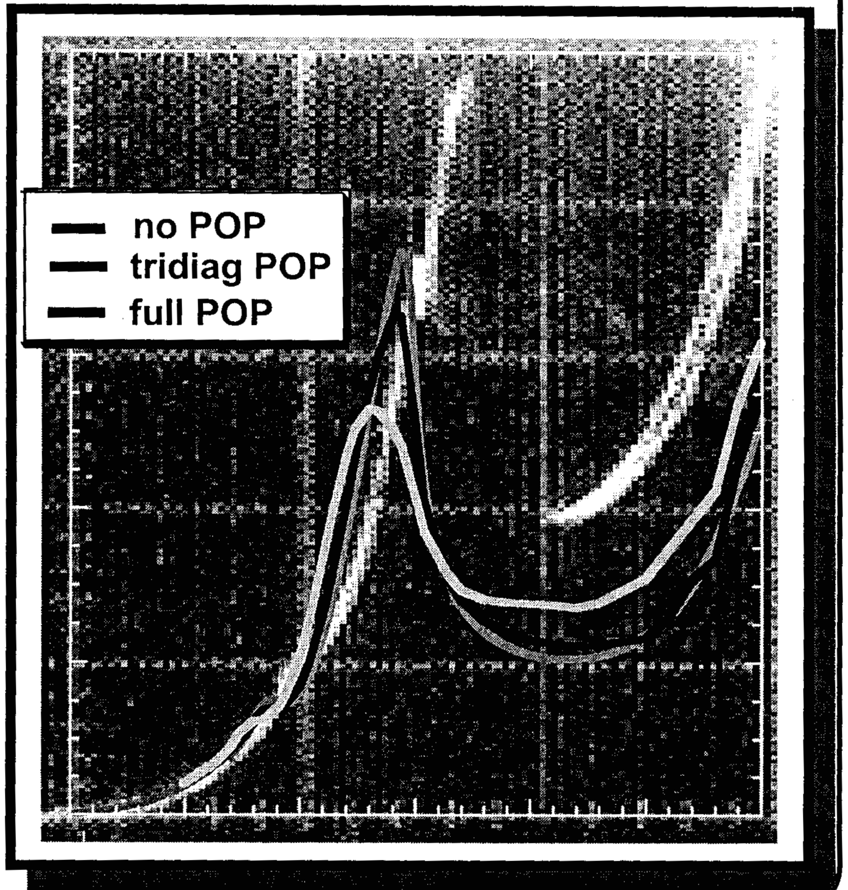

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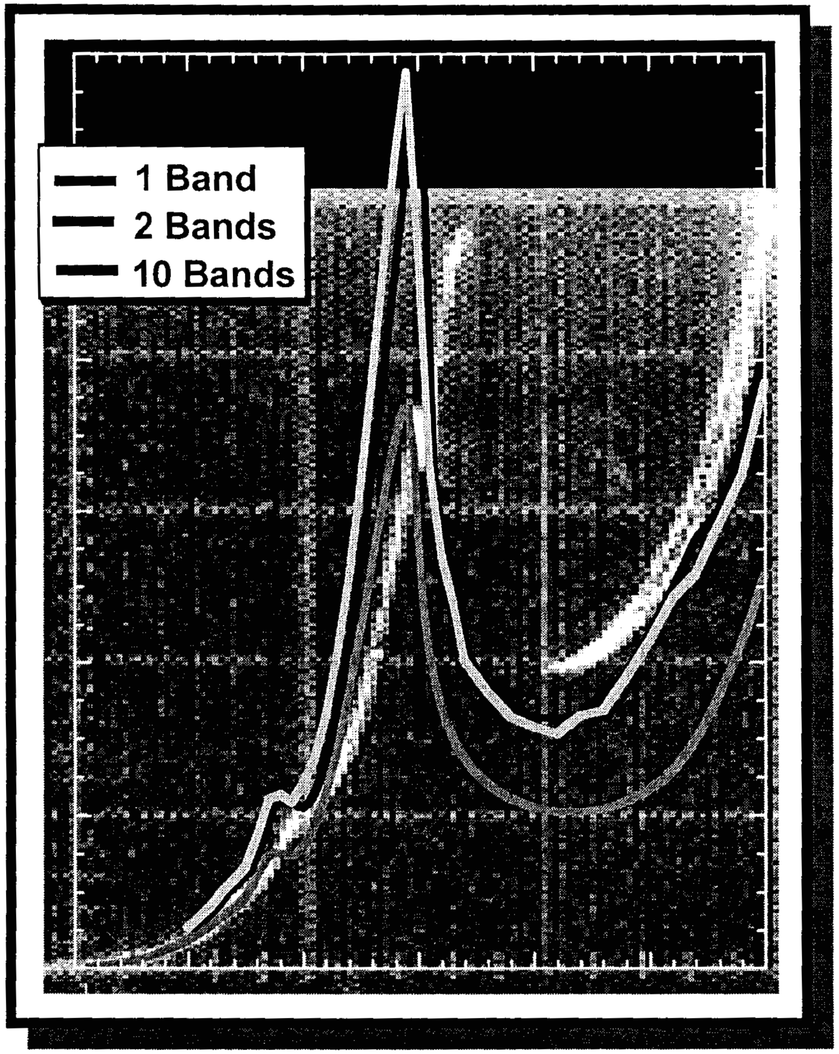
Single Band vs. Multiband

Multiband without scattering



Single band with scattering

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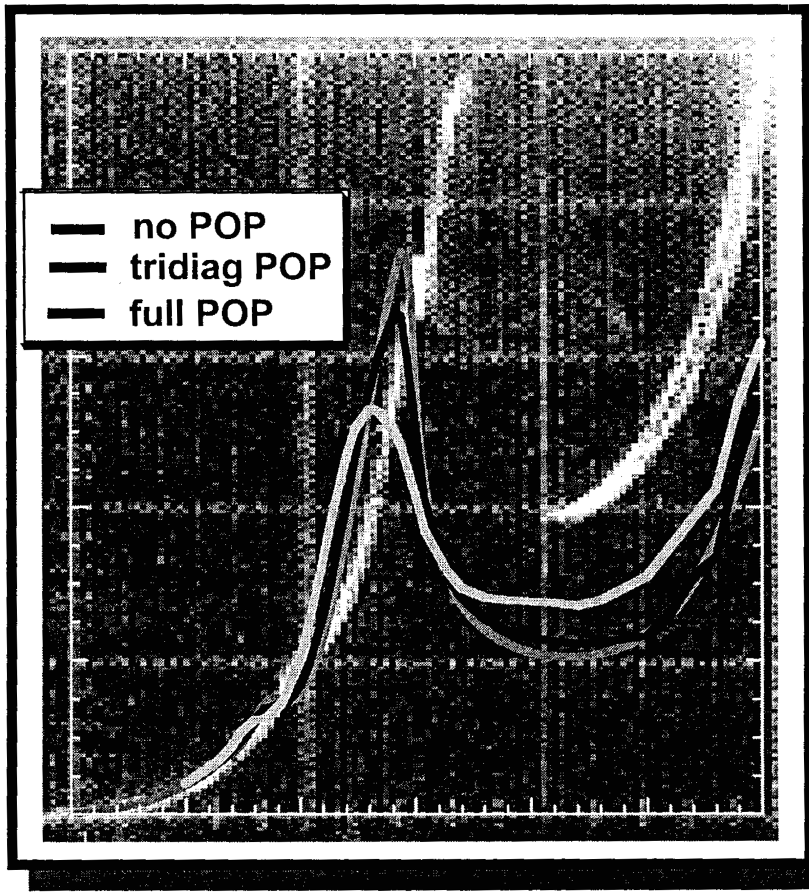

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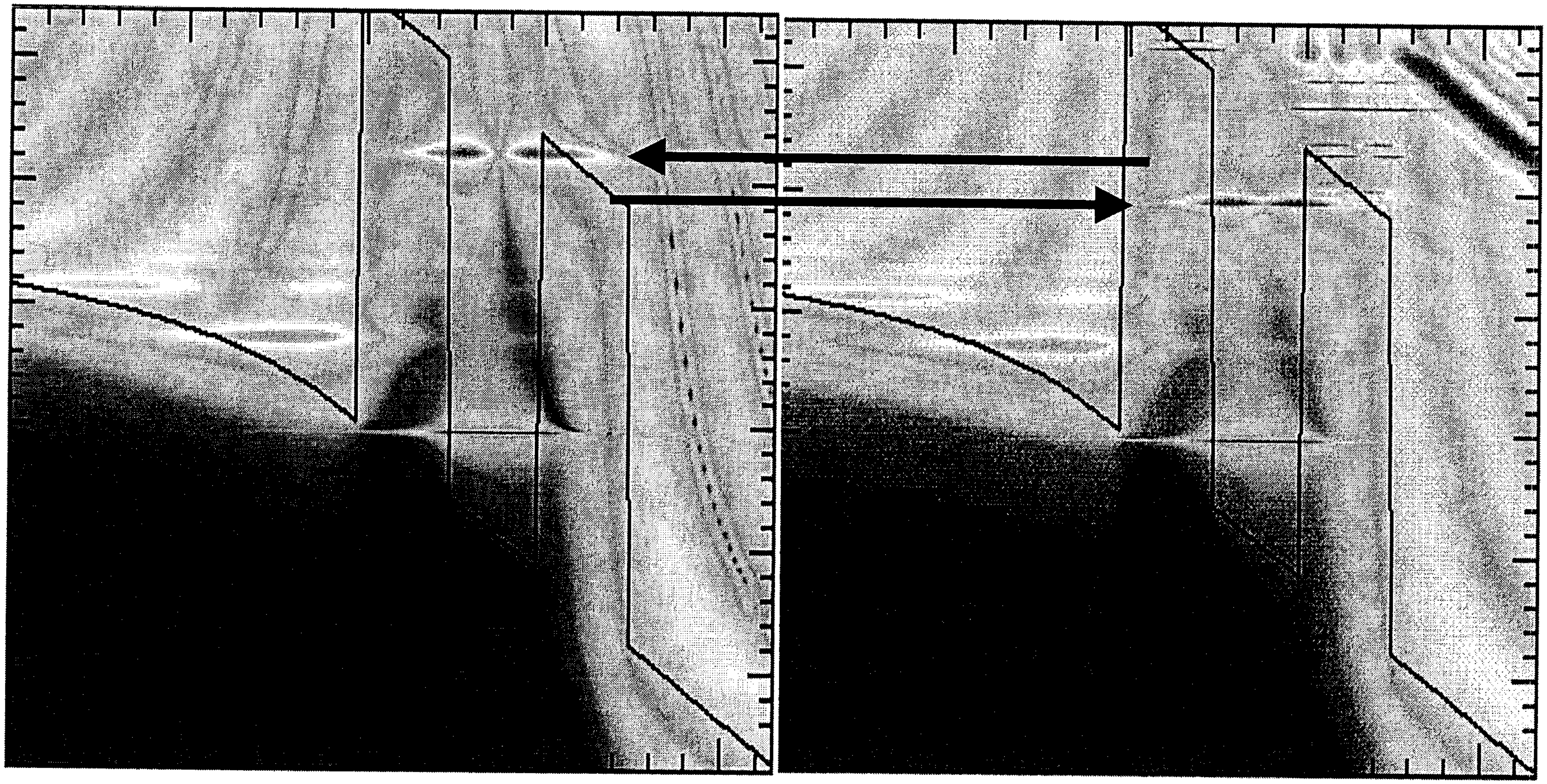
Comparison of 1 and 10 Band Densities of States



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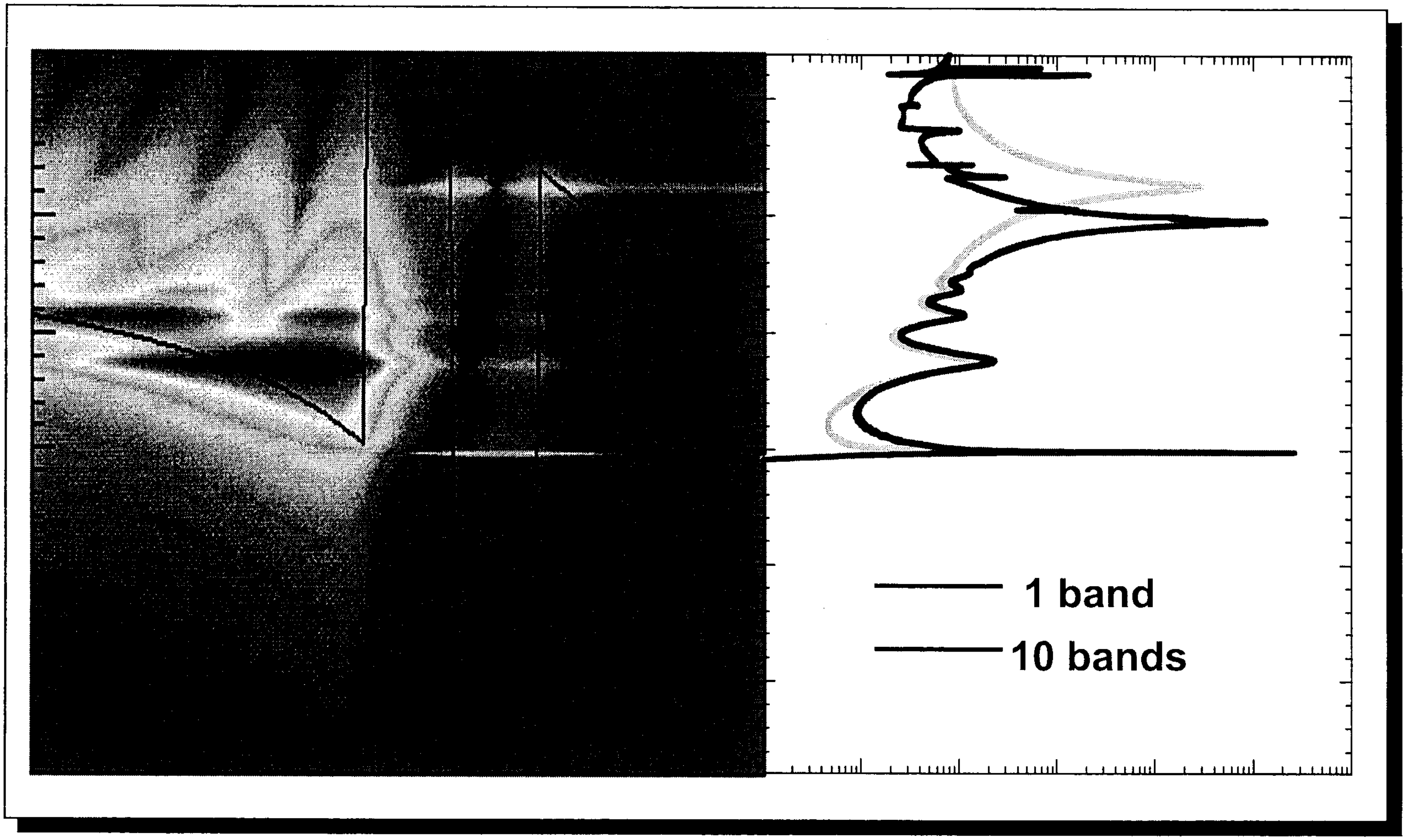
Current Flow through the Second Resonance



1 band electron density current density

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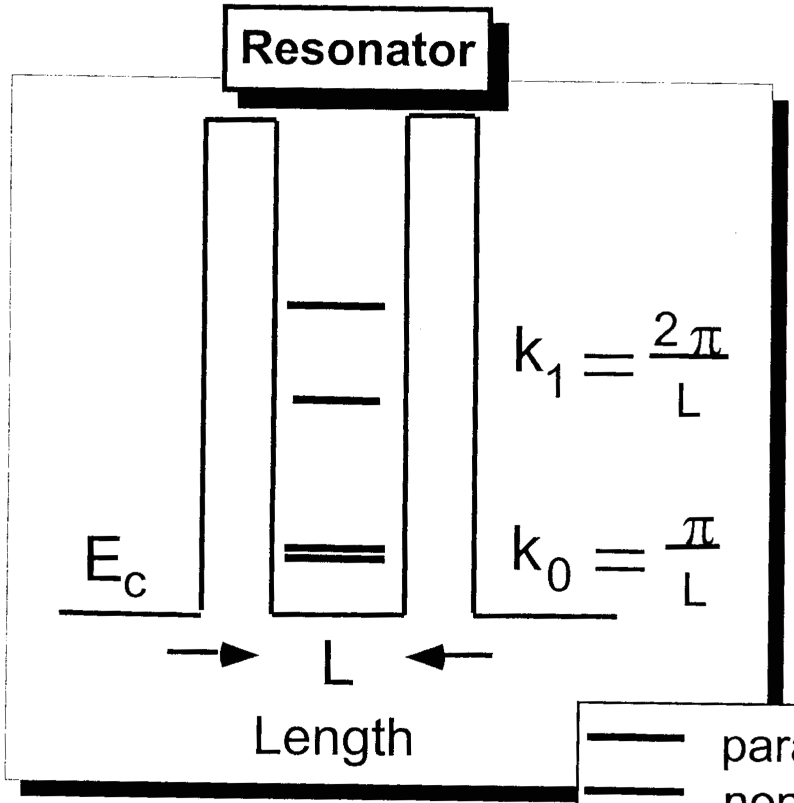
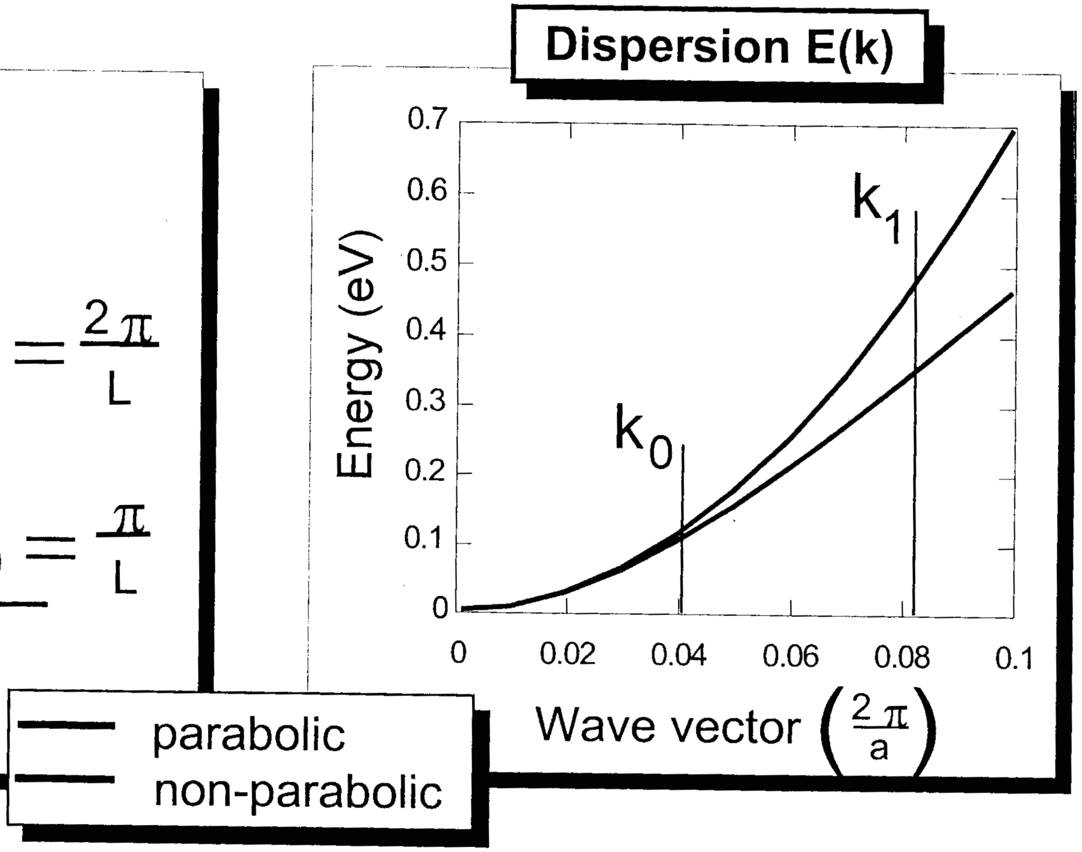
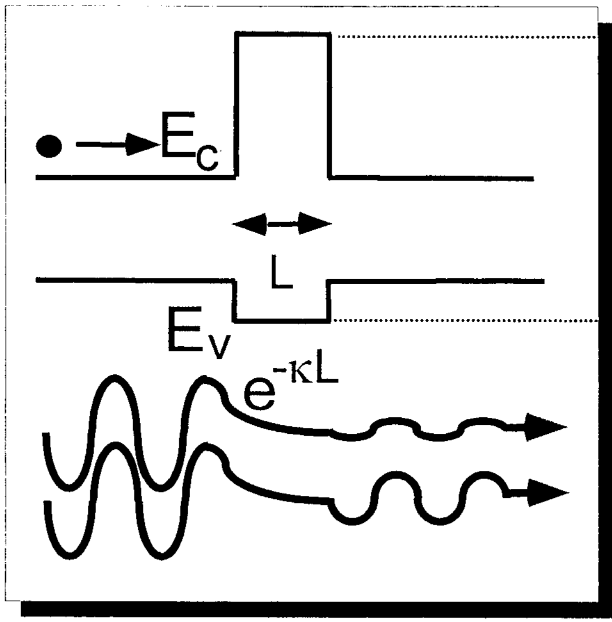
Resonance State Lowering due to Band Non-Parabolicity

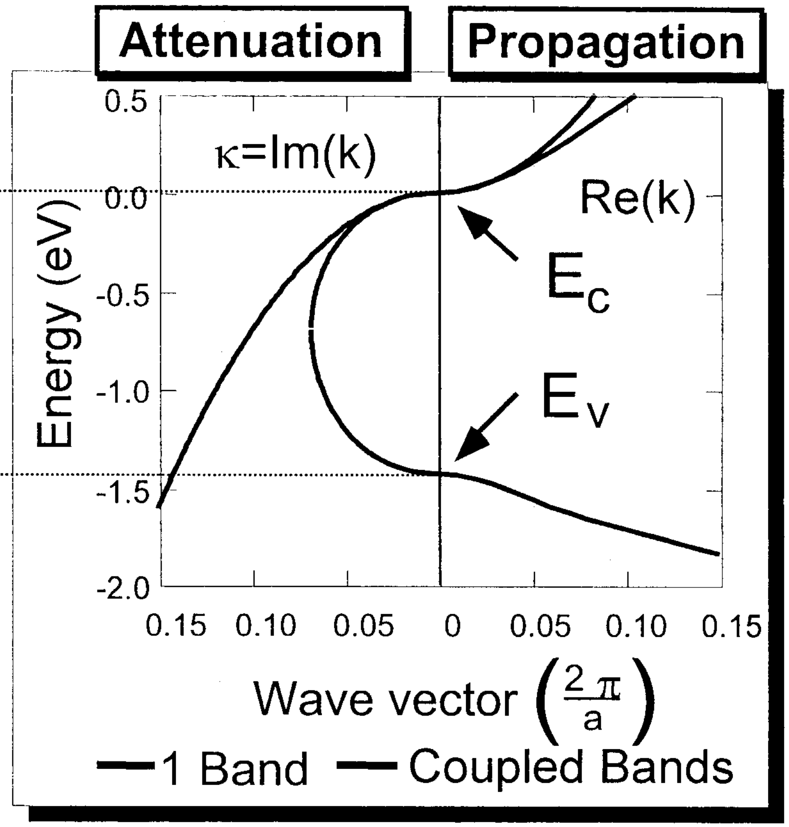




Second diode turn-on at lower voltages.

Wave Attenuation in Barriers

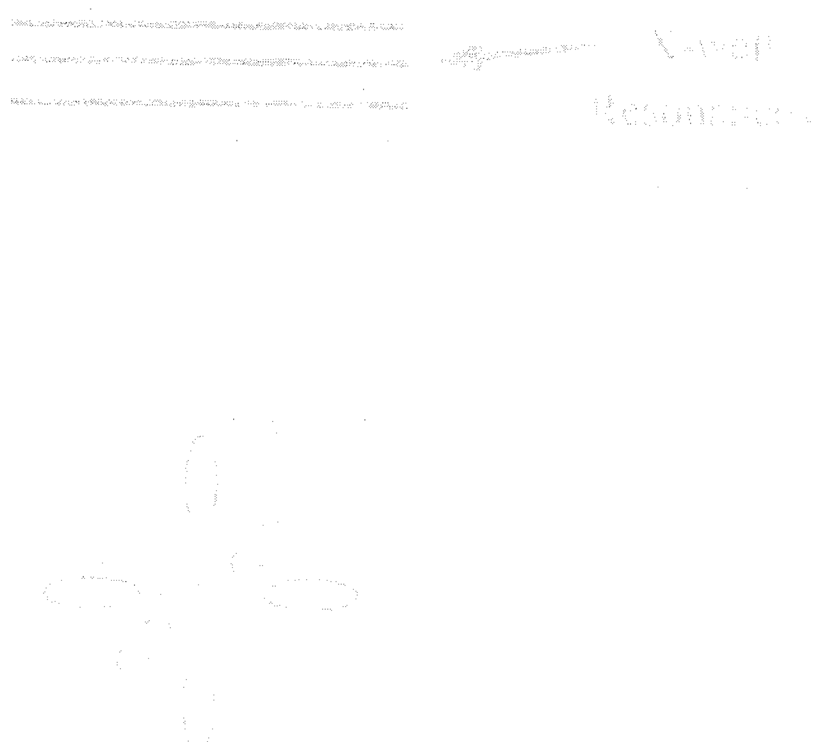




- Attenuation is smaller with coupled bands
- Tunneling probability increases
- Current increases

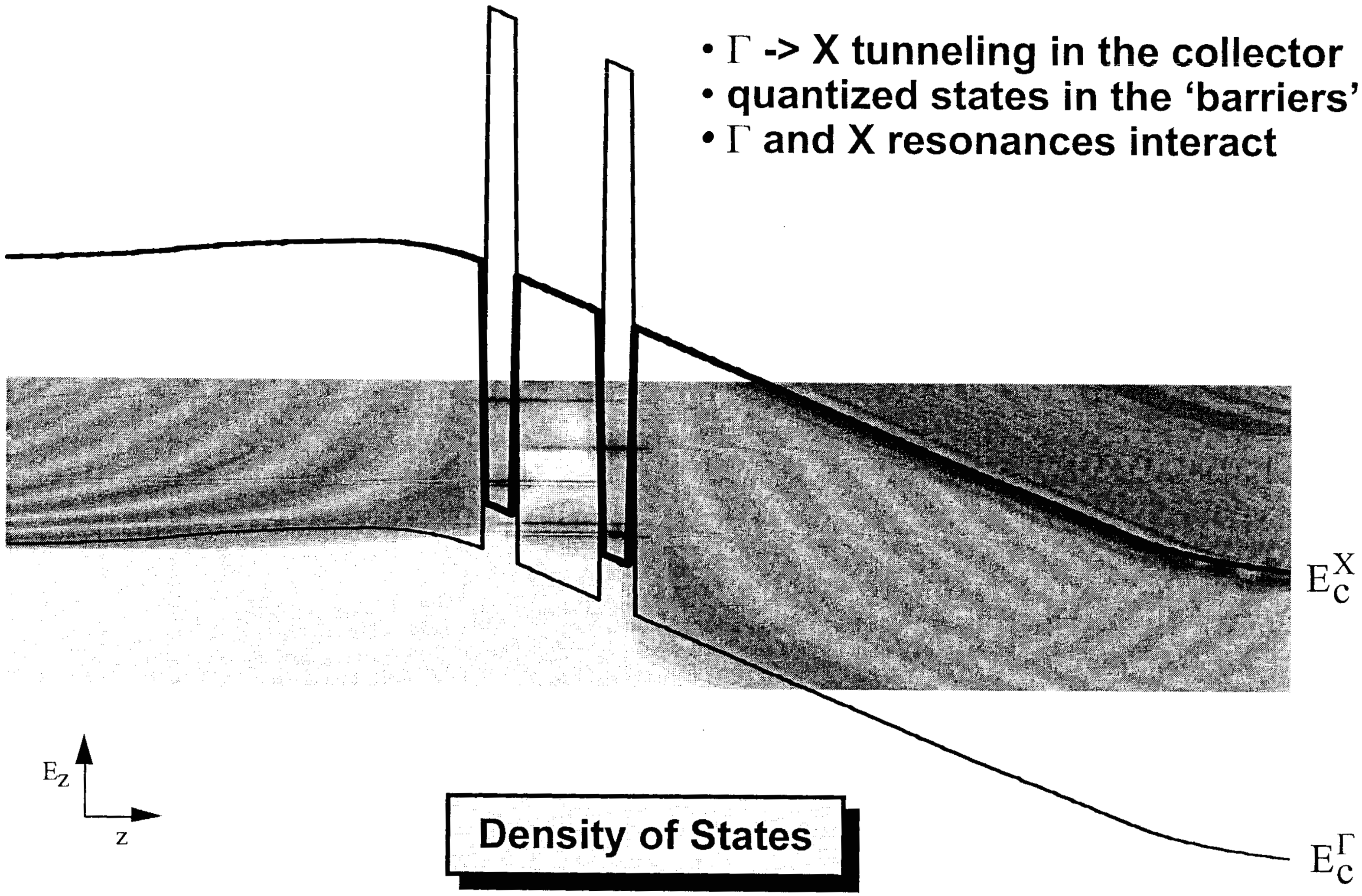
=> Barriers are more transparent than expected!!!

Transport in Indirect Gap Barriers



Multiband Effects in GaAs/AlAs RTD's

- Γ -> X tunneling in the collector
- quantized states in the 'barriers'
- Γ and X resonances interact



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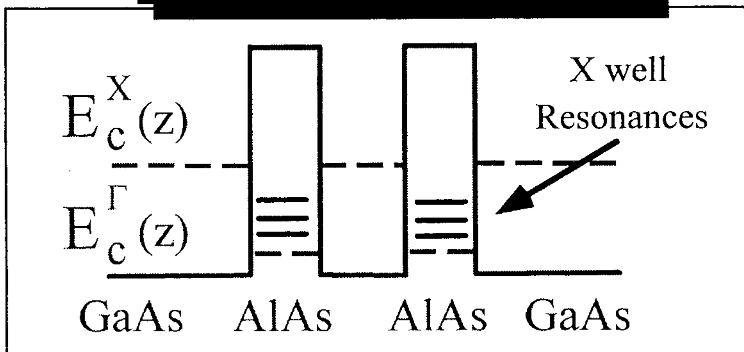
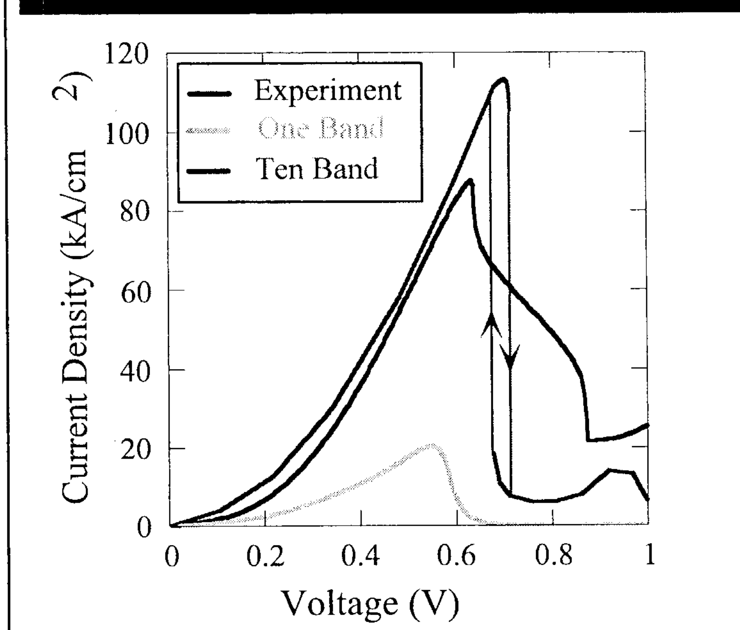
GaAs / AlAs RTD Simulation

Single Band Model

Multi-Band Model



Current Density vs. Voltage



Agreement between simulation and experiment has significantly improved with the addition of band structure effects.

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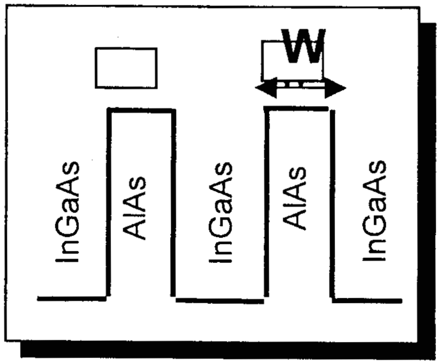
Testmatrix-Based Verification (room temperature)

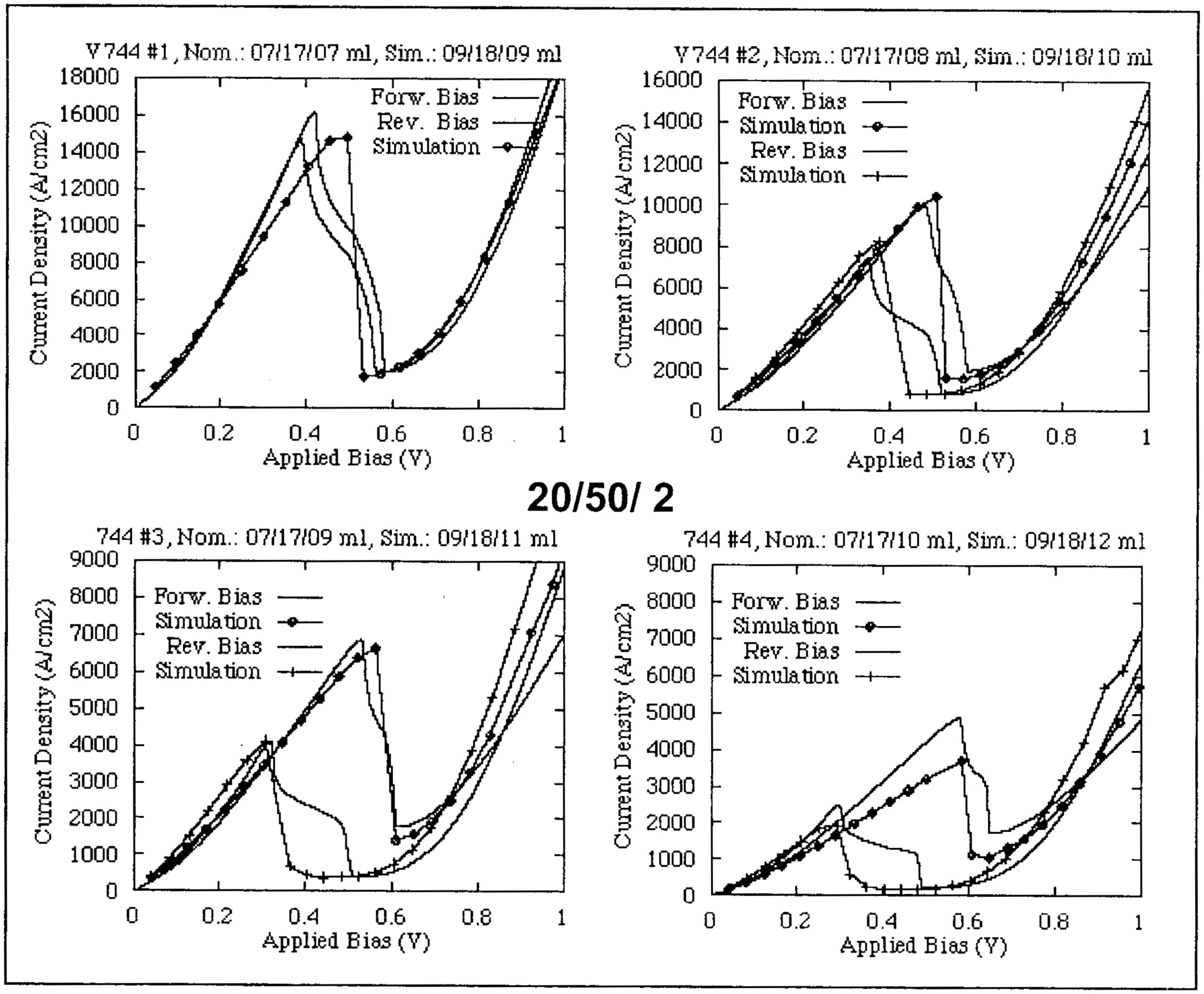
Strained InGaAs/AlAs 4 Stack RTD with Asymmetric Barrier Variation

Vary One Barrier Thickness



Four increasingly asymmetric devices:

20/50/20 Angstrom
20/50/23 Angstrom
20/50/25 Angstrom
20/50/27 Angstrom



Genetically Engineered Nanoelectronic Structures (GENES)

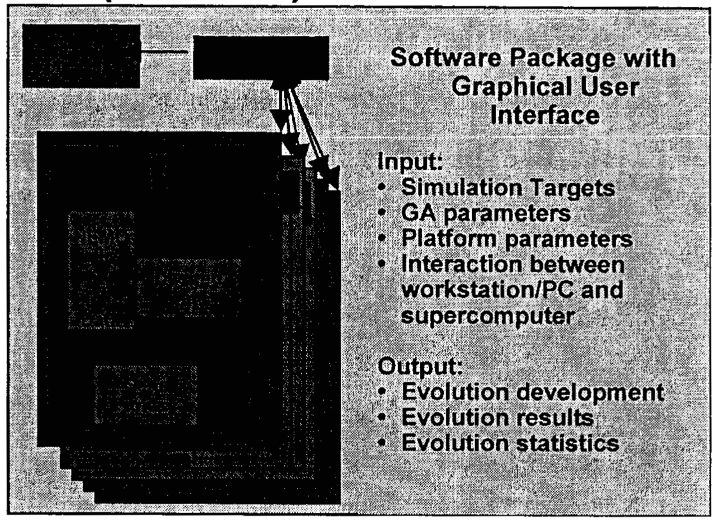
Objectives:

- Automate nanoelectronic device synthesis, analysis, and optimization using genetic algorithms (GA).

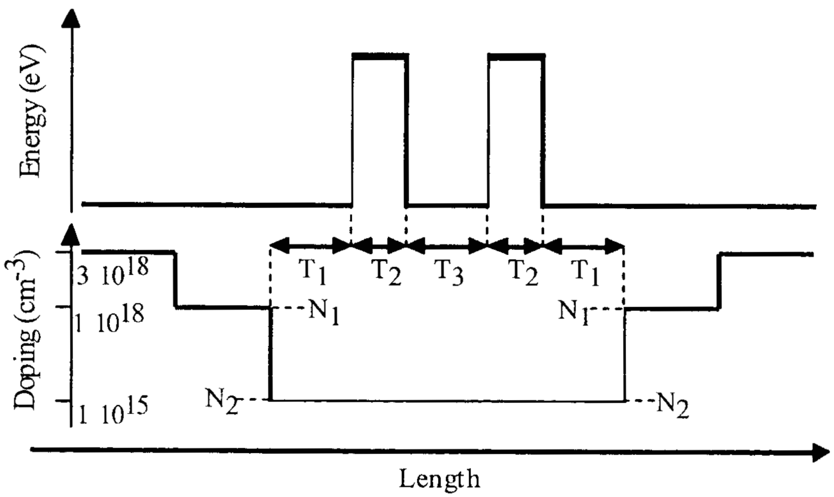
Approach:

- Augment parallel genetic algorithm (PGApack).
- Combine PGApack with NEMO.
- Develop graphical user interface for GA.

Architecture

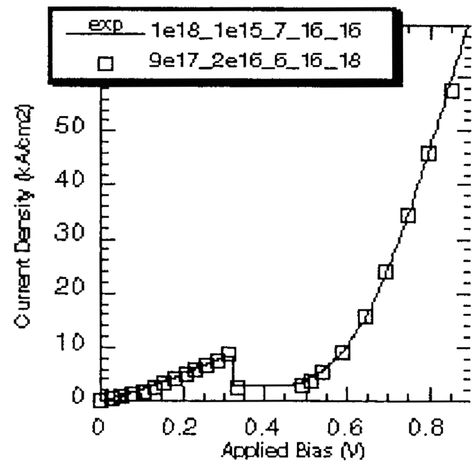


How do you know what you have built?



Results:

Nanoelectronic Device Structural analysis



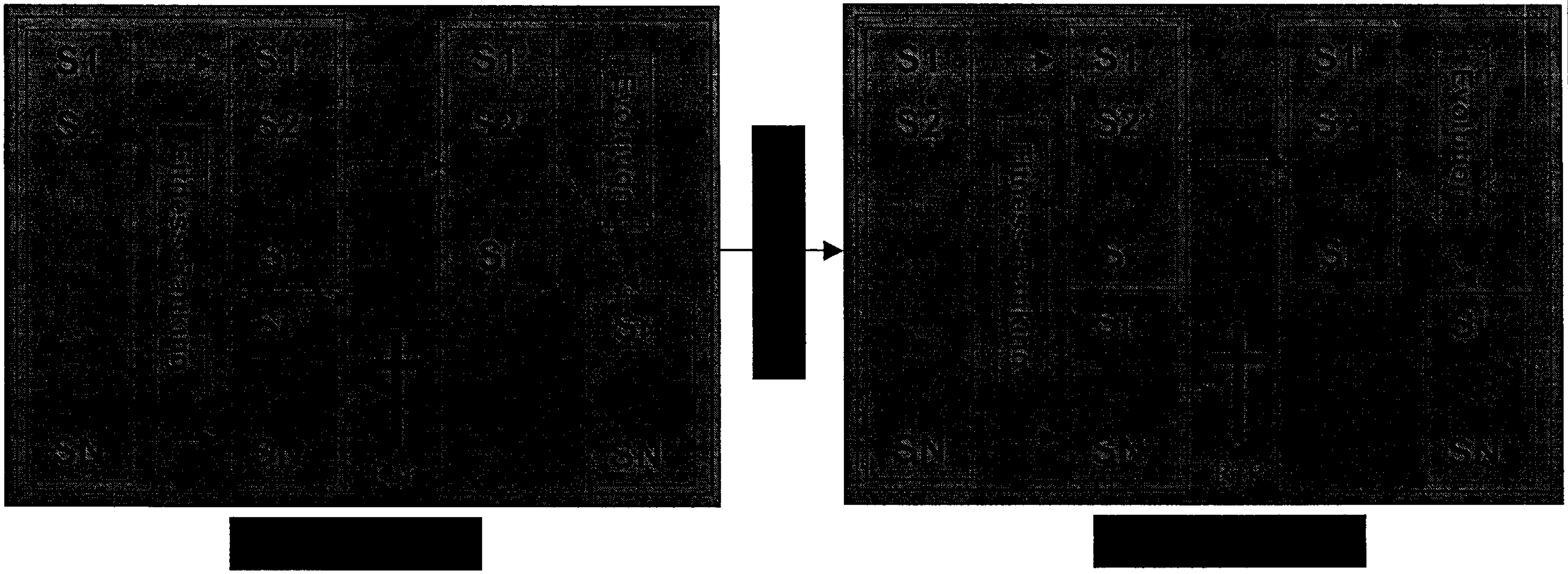
GA analyzed atomic monolayer structure and doping profile of RTD device

Black: structure specs, Blue: Best fit

Key Elements to NEMO Conclusions

- **NEMO Goals Achieved:**
  - Quantitative design and synthesis of resonant tunneling diodes (RTD's).
  - Faster simulation than experimental turn-around (1 week).
- **Lessons Learned:**
  - Comprehensive theory approach really did work.
  - Needed close coupling to well controlled test matrices.
  - Contact treatment and full bandstructure approach brought breakthrough.
  - Scattering (in central RTD) was not the most important (against all predictions).
    Scattering in the contacts is the most important effect, but we need to fake it through relaxation time approximation.
  - Can perform automated device synthesis and analysis.

Basic Genetic Algorithm



- Genetic algorithm parameter optimization is based on:
  - Survival of good parameter sets
  - Evolution of new parameter sets
  - Survival of a diverse population

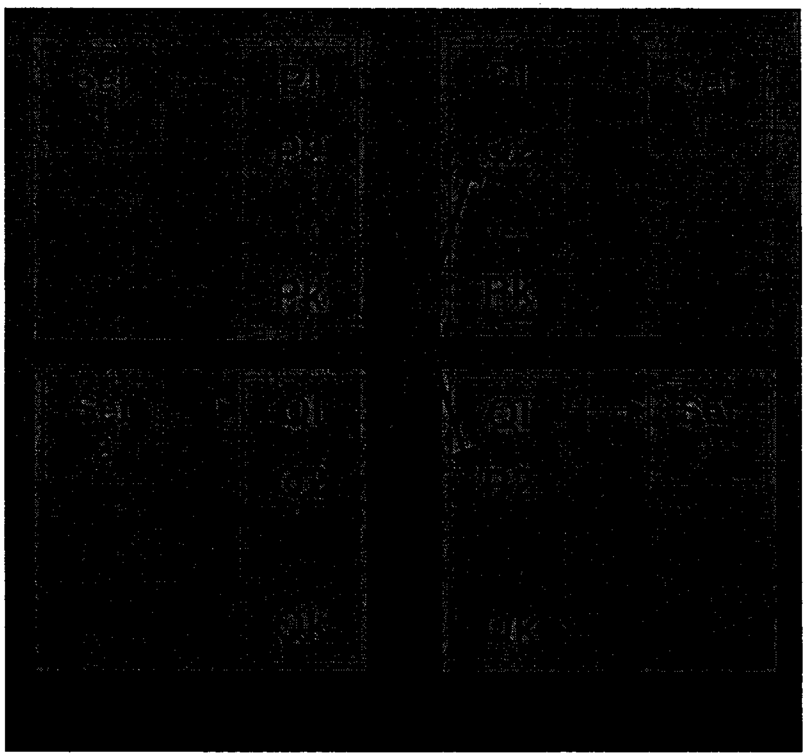
- Optimization can be performed globally, rather than locally.

Basic Evolution Operations

Each set (Si) consists of several parameters (Pj)

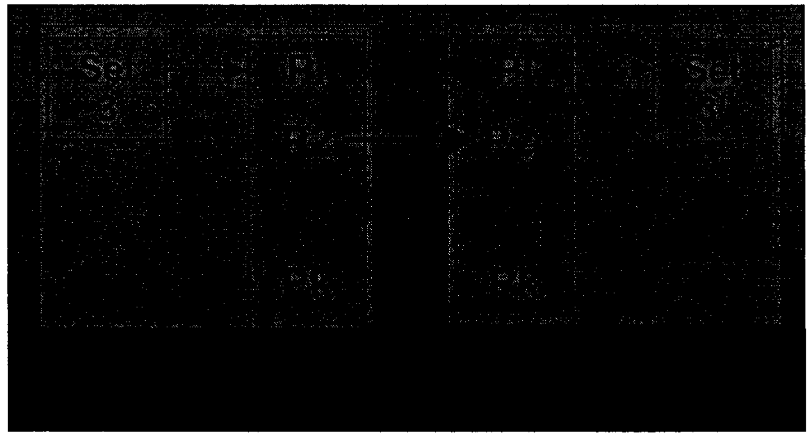
The parameters Pj can be of different kinds: real, integers, symbols.

Gross Exploration



Crossover explores different combinations of existing

Fine Tuning

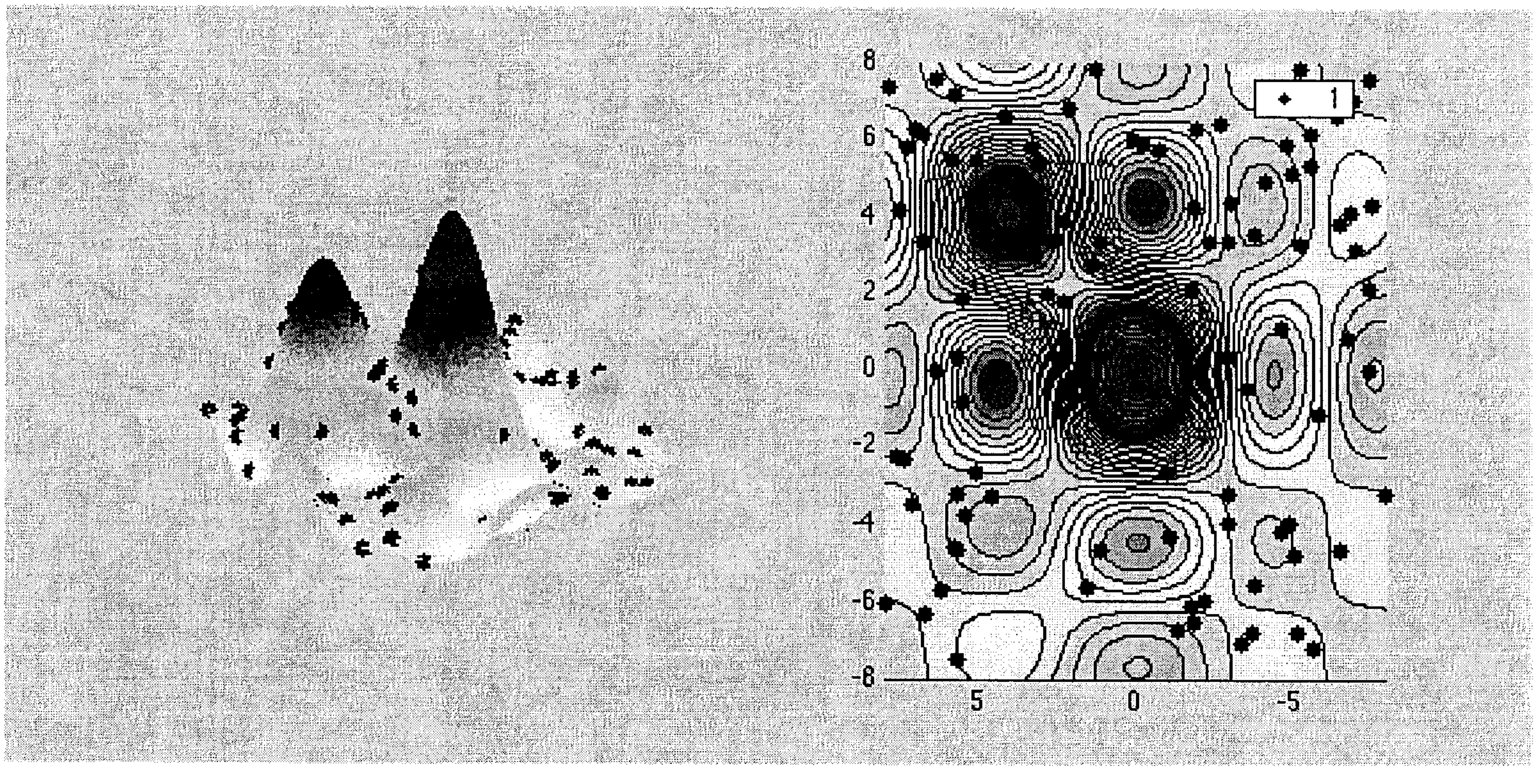


- **Creation of new gene values.**

JPL

Global Optimization via Genetic Algorithms

$$F(x,y)=\frac{\sin(x)}{x}\frac{\sin(y)}{y}+0.7\frac{\sin(x-4)}{(x-4)}\frac{\sin(y-4)}{(y-4)}$$



JPL

Global Optimization: Genetic Algorithm Development

Genetic Algorithm Convergence

pop = 100, 300 generations, steady-state (10%), 2-point crossover p = 0.85, mutatation p = 1/2

QuickTime™ and a
Video decompressor
are needed to see this picture.

JPL

Outline:
Key Elements to NEMO

- Unexpected / Breakthroughs:
  - Treatment of extended contact regions

Outline: Key Elements to NEMO

- Unexpected / Breakthroughs:
  - Full bandstructure
    Non-parabolicity
    band warping
    indirect materials

Outline:
Key Elements to NEMO

- **NEMO Goal:**
  - Quantitative design and synthesis of resonant tunneling diodes (RTD's).
  - Faster simulation than experimental turn-around (1 week).
- **Anticipated / Expected:**
  - Scattering - origin of the valley current.
  - Charge self-consistency - position of voltage peak.
- **Unexpected / Breakthroughs:**
  - Treatment of extended contact regions
  - Full bandstructure - Empirical tight binding: sp3s*, sp3d5s*
    - Non-parabolicity, complex band warping, indirect gaps
- **Putting it all together**
  - NEMO - testmatrix
  - **The next step: automated analysis and SYNTHESIS**